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## Functionalization of fullerene materials toward applications in perovskite solar cells†

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Fullerene materials exhibit high electron affinity, high electron mobility and small reorganization energy, thus they have been widely utilized as electron transport layers, cathode interfacial layers and trap passivators in constructing efficient organic–inorganic hybrid halide perovskite solar cells (PSCs). Herein, we summarize the recent progress of functionalized fullerene materials (*i.e.*, fullerene derivatives) which have been applied in PSCs, focusing on chemical functionalization strategies. We provide exhaustive lists of all reported fullerene derivatives applied in PSCs, and categorize them based on the types of addend groups and addition patterns. In particular, we manage to unveil the correlation between the chemical structures of fullerene derivatives, especially the addend groups, and their performance in improving the PSC device efficiency and stability. Finally, we propose an outlook on the future development of fullerene derivatives in realizing high-performance PSC devices.

## 1. Introduction

Organic–inorganic hybrid halide perovskites with a general formula of  $ABX_3$  (Fig. 1a), where  $A^+$  is  $CH_3NH_3^+$ ,  $NH_2CH=NH_2^+$ ,

$CS^+$ ,  $Rb^+$  *etc.*,  $B^{2+}$  is  $Pb^{2+}$  or  $Sn^{2+}$  and  $X^-$  is  $I^-$ ,  $Br^-$  or  $Cl^-$ , are emerging optoelectronic materials with the advantages of tunable optical bandgaps, high absorption coefficients, long charge carrier diffusion lengths, small exciton binding energies, and high carrier mobilities; thus they have been receiving considerable attention in the widespread fields of photovoltaics, light-emitting diodes, sensors and photodetectors *etc.*<sup>1–7</sup> In particular, since the first demonstration of applying  $CH_3NH_3PbX_3$  ( $X = Br, I$ ) in dye-sensitized solar cells as sensitizers in 2009,<sup>8</sup> perovskite solar cells (PSCs) using the organic–inorganic hybrid halide perovskites as light-absorbing layers

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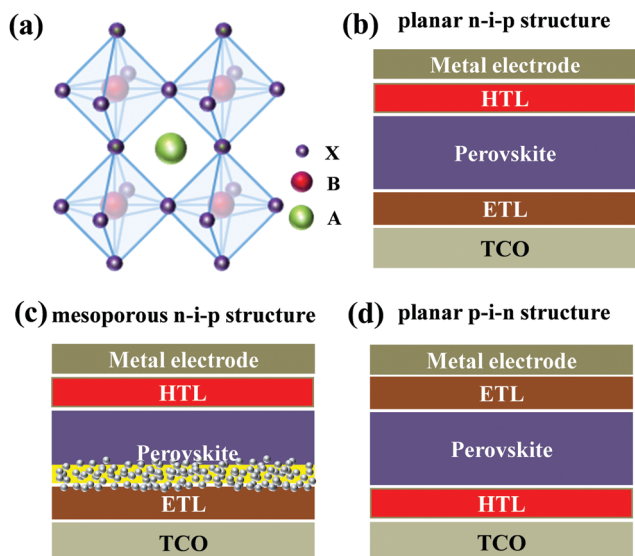
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**Fig. 1** (a) Crystal structure of ABX<sub>3</sub> perovskite light-absorbing materials. The common device architectures of (b) planar n-i-p structures, (c) mesoporous n-i-p structures, and (d) planar p-i-n structures. TCO refers to transparent conductive oxide.

have been rapidly developed during the past decade, and the record certified power conversion efficiency (PCE) has reached 25.2%.<sup>9</sup> Such a high PCE becomes competitive with the commercialized crystalline-Si and inorganic semiconductor thin film solar cells, rendering bright prospects of PSCs toward efficient utilization of sustainable energy.<sup>10</sup>

For the state-of-the-art PSC devices, their architectures can be generally categorized into three main types: mesoporous n-i-p structures, planar n-i-p structures and planar p-i-n structures (Fig. 1b–d), where n refers to an n-type semiconductor functioning as an electron transporting layer (ETL), i represents a perovskite, and p denotes a p-type semiconductor acting as a

hole transporting layer (HTL).<sup>11–15</sup> Although tremendous advances have been accomplished for PSCs during the past decade, further improvements of both device efficiency and stability are still urgently desired so as to meet the requirement of large-scale commercial applications. Besides, up to now high-efficiency PSC devices are mostly achieved for lead (Pb)-based perovskites, and the environmental toxicity of Pb raises another challenge of PSC application.<sup>16</sup>

To improve the PSC device efficiency and stability, modulating the composition, phase and morphology of perovskite light-absorbing layers and engineering the perovskite/electrode interfaces has been implemented in addition to optimizing the device structure.<sup>17–25</sup> For these strategies, since fullerene materials exhibit high electron affinity, high electron mobility and small reorganization energy, fullerenes have been widely utilized in PSCs by means of being incorporated as interfacial materials between perovskite layers and electrodes or as additives within perovskite layers. In this way, fullerenes behave as electron transport layers, cathode interfacial layers or trap passivators.<sup>6,14,26</sup> Interestingly, versatile roles of fullerenes in PSCs have been identified, revealing that fullerenes can not only facilitate electron extraction and transport due to the strong electron-accepting ability upon being incorporated as interfacial modification layers, but can also lead to defect passivation on the perovskite surface and grain boundaries when introduced as additives within perovskite layers.<sup>27–29</sup>

In this review, we present a comprehensive summary on recent advances in applications of functionalized fullerene materials (*i.e.*, fullerene derivatives) in PSCs. Although there have been several review papers related to applications of fullerenes in PSCs as well, these papers either cover broad topics such as both organic and perovskite solar cells or emphasize merely single aspects,<sup>6,14,26,30–32</sup> while a dedicated review focused on chemical functionalization strategies of fullerene derivatives and the correlations between their chemical structures, especially the addend groups, and functions in PSCs is desirably needed. Herein, we emphasize the synthetic strategies of fullerene derivatives and the importance of their addend groups in improving the performance of PSCs. Based on exhaustive lists of all reported fullerene derivatives applied in PSCs, we categorize them into five groups according to the types of addend groups and addition patterns. In particular, we manage to unveil the correlation between the chemical structures of fullerene derivatives, especially the addend groups, and their performance in improving the PSC device efficiency and stability. Finally, we propose our perspective on the future development of fullerene derivatives in realizing high-performance PSC devices.

## 2. PC<sub>61</sub>BM and PC<sub>61</sub>BM-based fullerene derivatives

[6,6]-Phenyl C<sub>61</sub>-butyric acid methyl ester (PC<sub>61</sub>BM, Fig. 2) is the most widely used ETL of p-i-n (*i.e.*, inverted-structure) PSCs, and was first applied by Chen and co-workers in 2013. PC<sub>61</sub>BM possesses a suitable lowest unoccupied molecular orbital (LUMO) energy level, which matches with the valence band



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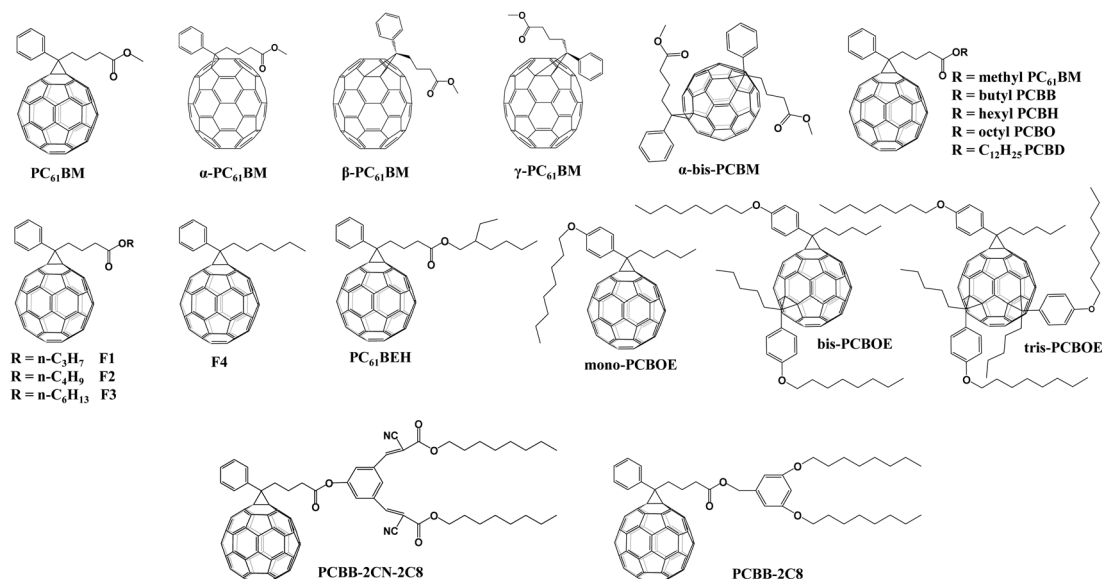


Fig. 2 Molecular structures of PC<sub>61</sub>BM and PC<sub>61</sub>BM-based fullerene derivatives applied in PSCs.

energy level of CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite, leading to enhanced electron transport from the perovskite layer to the PC<sub>61</sub>BM ETL. As a result, a PCE of 3.9% was achieved for p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSC devices.<sup>33</sup> In 2014, Huang and co-workers found that PC<sub>61</sub>BM deposited on top of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> layer can reduce the trap-states of perovskite films by two orders of magnitude (Fig. 3a), resulting in a moderate PCE of 14.9% for PSC devices along with suppressed photocurrent hysteresis.<sup>34</sup> Later on, the

same group reported that reducing the disorder of the PC<sub>61</sub>BM layer by a simple solvent annealing method (Fig. 3b) is beneficial to increase the open-circuit voltage ( $V_{oc}$ ) of CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSC devices without sacrificing either short-circuit current ( $J_{sc}$ ) or the fill factor (FF). This study further pointed out that the ordered PC<sub>61</sub>BM assembly leads to a significant decrease in the electronic density of states along with an increase in the quasi-Fermi level of the photogenerated electrons ( $E_{Fn}$ ), contributing

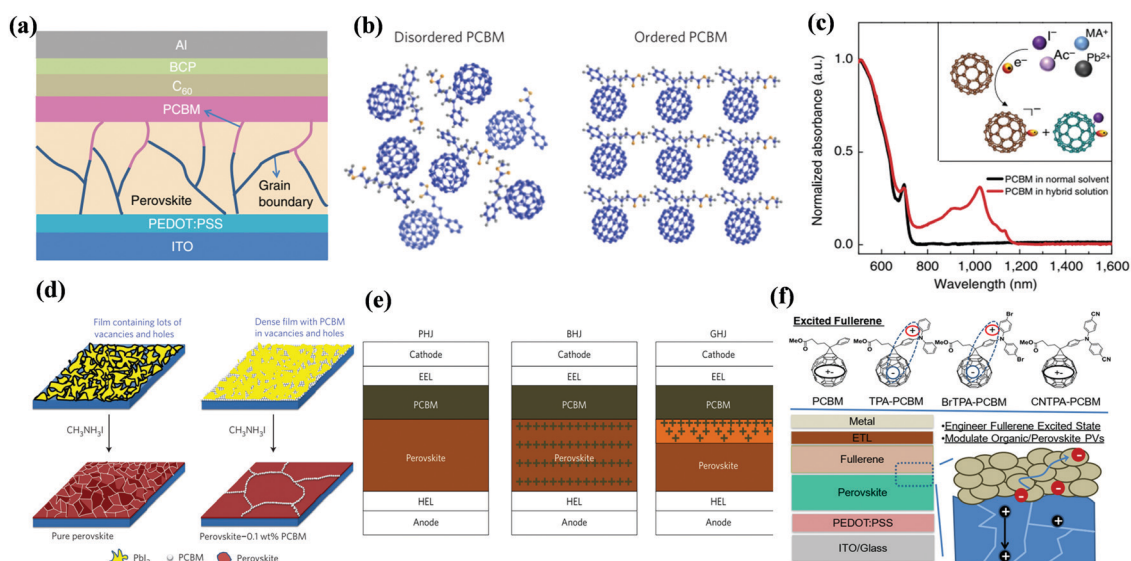


Fig. 3 (a) Device structure of p-i-n perovskite solar cells with a PC<sub>61</sub>BM layer. Reproduced with permission from ref. 34. Copyright 2014, Nature Publishing Group. (b) Schematic of disordered and ordered PC<sub>61</sub>BM structures and energy disorder of the PC<sub>61</sub>BM layer influences the device  $V_{oc}$ . Reproduced with permission from ref. 35. Copyright 2016, Nature Publishing Group. (c) Halide-induced deep trap *in situ* passivation and ultraviolet-visible absorption spectroscopy of the interaction between PC<sub>61</sub>BM and the perovskite in different solutions. Reproduced with permission from ref. 28. Copyright 2015, Nature Publishing Group. (d) Formation of perovskite grains with and without PC<sub>61</sub>BM. Reproduced with permission from ref. 42. Copyright 2016, Nature Publishing Group. (e) Three types of inverted PSCs with a mixed and graded interlayer. Reproduced with permission from ref. 44. Copyright 2016, Nature Publishing Group. (f) Chemical structures of fullerene derivatives and the CT characters of them deposited atop perovskite films. Reproduced with permission from ref. 51. Copyright 2015, Royal Society of Chemistry.

to the improvements of both  $V_{oc}$  and PCE (19.4%).<sup>35</sup> Thereafter, PC<sub>61</sub>BM became the most commonly used ETL of p-i-n PSCs.<sup>36–38</sup>

[6,6]-Phenyl C<sub>71</sub>-butyric acid methyl ester (PC<sub>71</sub>BM) as the cousin of PC<sub>61</sub>BM (Fig. 2) was also applied as an effective ETL in inverted-structure CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs in 2014, leading to an improved PCE of 16.31% that resulted from the remarkably higher  $V_{oc}$  of 1.05 V and FF of 0.78 relative to that based on PC<sub>61</sub>BM ETL (9.92%).<sup>39</sup> Later on, Xie and co-workers developed a formulation engineering method to study the effect of different component distribution ratios of PC<sub>71</sub>BM isomers ( $\alpha$ -,  $\beta_1$ - and  $\beta_2$ -PC<sub>71</sub>BM, Fig. 2) on the performance of p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. The PC<sub>71</sub>BM ETL with the optimized ratio of three isomers of PC<sub>71</sub>BM ( $\alpha$ : $\beta_1$ : $\beta_2$  = 17:1:2) exhibits the highest PCE of 17.56%, which outperformed those of the devices with isomerically pure PC<sub>71</sub>BM ETLs and other adducts of uncontrolled isomeric ratios due to the reduced molecular aggregation and improved electron transfer.<sup>40</sup>

In addition to acting as an ETL, PC<sub>61</sub>BM has also been introduced into the perovskite layer as an additive to construct bulk-heterojunction (BHJ) PSCs. In 2015, Sargent *et al.* first reported that PC<sub>61</sub>BM as an additive was added into the perovskite precursor to construct regular-structure (n-i-p) bulk-heterojunction PSCs. Since the molecular size of PC<sub>61</sub>BM is large, the possibility of becoming interstitial species within the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite layer can be precluded, therefore PC<sub>61</sub>BM addition leads to homogeneous distribution at the grain boundaries within the perovskite layer. The rich-assembly of PC<sub>61</sub>BM at the grain boundaries is beneficial to passivate the iodide-rich trap sites (PbI<sub>3</sub><sup>−</sup> antisite defects) through the formation of a PC<sub>61</sub>BM-halide radical (Fig. 3c), resulting in reduced anion migration and suppressed current-voltage hysteresis of PSCs.<sup>28</sup> The conception of BHJ-PSCs *via* PC<sub>61</sub>BM was further testified by Gong and co-workers in 2015. BHJ-PSCs formed *via* adding PC<sub>61</sub>BM into the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite precursor afforded an improvement in PCE from 6.9% to 12.78% owing to the improved perovskite crystallinity and enhanced “donor/acceptor” interfaces of the perovskite and PC<sub>61</sub>BM.<sup>41</sup> One year later, Wu and coworkers reported a two-step spin-coating method to construct CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>-PC<sub>61</sub>BM p-i-n BHJ-PSCs, revealing that PC<sub>61</sub>BM filled at the grain boundaries and vacancies of the perovskite films (Fig. 3d). The as-prepared p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> BHJ-PSCs delivered an improved PCE of 16.0% with an outstanding fill factor of 0.82 and no photocurrent hysteresis, attributed to the long charge diffusion length, balanced electron and hole mobilities and higher conductivity of the perovskite-PC<sub>61</sub>BM BHJ film.<sup>42</sup>

In addition to improving the device efficiency, constructing BHJ perovskite layers *via* PC<sub>61</sub>BM additives is also beneficial to enhance the thermal stability of PSC devices. In 2017, Cho and co-workers fabricated inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> BHJ-PSCs with PC<sub>61</sub>BM as an additive, unveiling that PC<sub>61</sub>BM located at perovskite grain boundaries markedly improved the thermal stability of the devices and suppressed the decomposition of the perovskite. This was due to the decreased grain interface area and the impeded migration of the halogen ions within the

perovskite lattice through electron transfer from the halogen ions to PC<sub>61</sub>BM.<sup>43</sup> In 2016, Han *et al.* constructed a perovskite-fullerene graded heterojunction (GHJ) by dripping PC<sub>61</sub>BM dissolved in the anti-solvent toluene onto the upper formamidinium (FA) cation-containing perovskite layer, achieving a certified efficiency of 18.21% with a large area of 1.022 cm<sup>2</sup> (Fig. 3e).<sup>44</sup>

Considering the superior performance of PC<sub>61</sub>BM as a mono-adduct in PSCs, an intriguing question is whether the bis-adduct of PC<sub>61</sub>BM performs better or not. In 2017, Grätzel and co-workers incorporated isomer-pure bis-PC<sub>61</sub>BM ( $\alpha$ -bis-PC<sub>61</sub>BM, Fig. 2) into a CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite film *via* an anti-solvent method, and found that  $\alpha$ -bis-PC<sub>61</sub>BM could act as a templating agent for enhancing the crystallinity of perovskite films, leading to a PCE of 20.8% for n-i-p BHJ-PSCs, which is improved relative to that based on PC<sub>61</sub>BM (19.9%). Besides, due to the increased hydrophobicity and crystallinity of the perovskite film induced by  $\alpha$ -bis-PC<sub>61</sub>BM, the device achieves a remarkable improvement of stability relative to that of PC<sub>61</sub>BM-based devices.<sup>45</sup>

The effect of the end alkyl group within PC<sub>61</sub>BM on its performance has also been investigated. A series of PC<sub>61</sub>BM analogues containing different end alkyl groups were synthesized and applied as ETLs by Bolink and co-workers so as to evaluate their hole blocking/electron transporting abilities for inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, revealing that the longer alkyl groups help to reduce the defects within fullerene layers.<sup>46</sup> A more in-depth investigation on the influence of PC<sub>61</sub>BM-analogues (Fig. 2) and C<sub>60</sub>MC<sub>12</sub> (see Fig. 15) ETLs on the performance of inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Br<sub>x</sub> PSCs was performed by Miyano and co-workers in 2018, showing that fullerene derivatives with suitable energy level and crystallinity regulation *via* alkyl length contribute to the improved device efficiency.<sup>47</sup> More recently, four PC<sub>61</sub>BM-like fullerene derivatives F1-F4 (Fig. 2) were applied by Troshin and co-workers as ETLs in inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, among which devices based on F1 containing *n*-propyl show the best ambient stability. The outstanding performance of the F1 ETL is due to the optimal alkyl length enabling the side chains to fill the gaps between fullerene spheres for preventing the diffusion of oxygen and moisture into the devices.<sup>48</sup>

Echegoyen and co-workers reported a novel PC<sub>61</sub>BM-analogue PC<sub>61</sub>BEH (Fig. 2) with a branched alkyl chain in 2018, which was applied as an ETL of inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, achieving an improved PCE relative to that of the control device based on the PC<sub>61</sub>BM ETL. Such an improved performance was attributed to the improved film morphology, enhanced defect passivation and electron extraction ability *via* the branched alkyl group.<sup>49</sup> Likewise, a series of mono-, bis- and tris-benzene octyl ether functionalized fullerene derivatives (PCBOEs, Fig. 2) were also synthesized and applied as ETLs in p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs as well. Increasing the number of adducts further decreases the electron mobility of PCBOEs which leads to charge accumulation at the perovskite/ETL interface, delivering a lower PCE than that of the PC<sub>61</sub>BM ETL.<sup>50</sup> In addition to the alkyl groups, Jen and co-workers synthesized a series of donor-acceptor fullerene derivatives by grafting triphenylamine (TPA) (Fig. 3f) onto the C<sub>60</sub> cage, and applied them as ETLs of inverted p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> PSCs. The intramolecular charge transfer from TPA to C<sub>60</sub> helps to

improve molecular polarization, carrier density, and charge transport/excitation capability, contributing to the improved device performance.<sup>51</sup>

Expect for the ETL, another role of PC<sub>61</sub>BM is to serve as a cathode modification layer to improve the performance of n-i-p PSCs.<sup>52</sup> A triblock fullerene derivative (PCBB-2CN-2C8, Fig. 2) was designed and synthesized by Yang and co-workers, which was applied as a cathode modification layer atop the TiO<sub>2</sub> ETL of the regular n-i-p CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. The rationally designed molecular structure of PCBB-2CN-2C8 fulfils multiple functions including: (a) the C<sub>60</sub> moiety possesses high electron affinity for efficient electron extraction and transfer; (b) the electron-deficient cyano-groups could passivate the oxygen vacancy of TiO<sub>2</sub> for decreasing the interface recombination; (c) the grafted dioctyloxy chains and cyano-groups on the fullerene cage were able to reduce the solubility of PCBB-2CN-2C8 in polar solvents, which is beneficial for orthogonal solution-processing. As a result PCBB-2CN-2C8 incorporation led to an improved PCE from 14.38% to 17.35% as well as suppressed hysteresis.<sup>53</sup>

Table 1 provides an exhaustive list of all reported PC<sub>61</sub>BM and PC<sub>61</sub>BM-based fullerene derivatives applied in PSCs. Although PC<sub>71</sub>BM may deliver a comparable device performance with the PC<sub>61</sub>BM ETL in p-i-n PSCs, the traditional chemical reaction may inevitably occur at different reactive sites of C<sub>70</sub> to afford a mixture of multiple isomers of PC<sub>71</sub>BM, and the blending ratio of these isomers would influence the device performance obviously. Therefore, based on these results, it is clearly shown that PC<sub>61</sub>BM is the most commonly used fullerene derivative, which plays three versatile roles including as an independent ETL, an interfacial modifier and an additive in either p-i-n or n-i-p PSCs. Tailoring the end alkyl groups appears to impose little effect on the LUMO energy level of the fullerene derivative, while involving donor group

acceptors such as triphenylamine can increase the LUMO energy level. Using bis-adducts of fullerene is another effective approach to raise the LUMO energy levels relative to that of monoadducts, leading to a better matching of energy level alignment, consequently facilitating charge transfer and affording a higher V<sub>oc</sub>. Hence, considering the complex synthetic procedure and high cost of PC<sub>61</sub>BM, developing novel fullerene derivatives *via* grafting other functional groups as alternatives to achieve higher device performance of PSCs is highly desirable.<sup>6,54</sup>

### 3. Lewis base functionalized fullerene derivatives

Unlike the PC<sub>61</sub>BM bearing ester groups and alkyl chains, grafting electron-rich groups (*i.e.*, Lewis bases) onto the fullerene cage leads to enhanced polarity for fullerene derivatives, rendering different mechanisms upon being applied in PSCs. So far the reported Lewis bases include amine, oligoether, crown-ether and heterocycles *etc.*

#### 3.1 Amino-functionalized fullerene derivatives

Amino groups as a representative Lewis base were extensively used to functionalize fullerenes. The reported amino groups include an amino (–NH<sub>2</sub>) group, a dimethylamino (–N(CH<sub>3</sub>)<sub>2</sub>) group and trimethylamine halide (–N<sup>+</sup>(CH<sub>3</sub>)<sub>3</sub>I<sup>–</sup>) ions, which were grafted onto the fullerene cage contributing to the formation of an Ohmic contact between the metal/perovskite interface by lowering the work function of the metal electrode. In addition, the strong electric dipole feature of amino-functionalized fullerene derivatives helps to form interfacial dipole layers, which are beneficial for forming built-in electric

**Table 1** An exhaustive list of all reported PC<sub>61</sub>BM and PC<sub>61</sub>BM-based fullerene derivatives applied in PSCs

| Compound                  | Active layer                                                                                 | LUMO <sup>a</sup> (eV) | μ <sup>b</sup> (cm <sup>2</sup> V <sup>–1</sup> s <sup>–1</sup> ) | Role of the molecule       | J <sub>sc</sub> (mA cm <sup>–2</sup> ) | V <sub>oc</sub> (V) | FF (%) | PCE (%) | Ref. |
|---------------------------|----------------------------------------------------------------------------------------------|------------------------|-------------------------------------------------------------------|----------------------------|----------------------------------------|---------------------|--------|---------|------|
| PC <sub>61</sub> BM       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.9                   | —                                                                 | ETL                        | 10.32                                  | 0.60                | 63     | 3.9     | 33   |
| PC <sub>61</sub> BM       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.9                   | —                                                                 | ETL                        | 22.6                                   | 1.13                | 75.0   | 19.4    | 35   |
| PC <sub>61</sub> BM       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | Additive                   | 18.0                                   | 1.086               | 75     | 14.4    | 28   |
| PC <sub>61</sub> BM       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | Additive                   | 20.2                                   | 0.97                | 82     | 16.0    | 42   |
| PC <sub>61</sub> BM       | FA <sub>0.85</sub> MA <sub>0.15</sub> Pb(I <sub>0.85</sub> Br <sub>0.85</sub> ) <sub>3</sub> | —                      | —                                                                 | Additive                   | 21.98                                  | 1.08                | 79     | 18.75   | 44   |
| PC <sub>71</sub> BM       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | ETL                        | 19.98                                  | 1.05                | 78     | 16.31   | 39   |
| α-Bis-PC <sub>61</sub> BM | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | Additive                   | 23.95                                  | 1.13                | 74     | 20.8    | 45   |
| PCBB                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.91                  | —                                                                 | ETL                        | 16.02                                  | 1.09                | 76     | 13.27   | 46   |
| PCBH                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.91                  | —                                                                 | ETL                        | 15.92                                  | 1.10                | 79     | 13.75   | 46   |
| PCBB                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Br <sub>x</sub>                           | –4.12                  | —                                                                 | ETL                        | 16.68                                  | 1.12                | 78     | 14.82   | 47   |
| PCBO                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Br <sub>x</sub>                           | –4.12                  | —                                                                 | ETL                        | 16.52                                  | 1.12                | 78     | 14.37   | 47   |
| PCBD                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Br <sub>x</sub>                           | –4.12                  | —                                                                 | ETL                        | 16.75                                  | 1.11                | 51     | 9.44    | 47   |
| F1                        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | ETL                        | 18.3                                   | 0.93                | 73     | 11.4    | 48   |
| F2                        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | ETL                        | 18.9                                   | 0.91                | 74     | 12.3    | 48   |
| F3                        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | ETL                        | 19.1                                   | 0.93                | 74     | 13.0    | 48   |
| F4                        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | —                      | —                                                                 | ETL                        | 20.6                                   | 0.90                | 79     | 14.6    | 48   |
| PC <sub>61</sub> BEH      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.89                  | 4.76 × 10 <sup>–4</sup>                                           | ETL                        | 22.5                                   | 0.95                | 77.61  | 16.26   | 49   |
| Mono-PCBOE                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.74                  | 8.8 × 10 <sup>–4</sup>                                            | ETL                        | 10.30                                  | 1.04                | 44.04  | 4.72    | 50   |
| Bis-PCBOE                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.65                  | 2.6 × 10 <sup>–4</sup>                                            | ETL                        | 2.13                                   | 1.03                | 65.98  | 1.39    | 50   |
| Tris-PCBOE                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –3.56                  | 2.7 × 10 <sup>–4</sup>                                            | ETL                        | 1.71                                   | 1.03                | 74.32  | 1.31    | 50   |
| TPA-PCBM                  | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Cl <sub>x</sub>                           | –3.69                  | 7.9 × 10 <sup>–4</sup>                                            | ETL                        | 10.87                                  | 0.88                | 69     | 17.71   | 51   |
| BrTPA-PCBM                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Cl <sub>x</sub>                           | –3.70                  | 3.3 × 10 <sup>–4</sup>                                            | ETL                        | 10.20                                  | 0.89                | 67     | 17.18   | 51   |
| CNTPA-PCBM                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Cl <sub>x</sub>                           | –3.72                  | 7.2 × 10 <sup>–5</sup>                                            | ETL                        | 5.60                                   | 0.90                | 48     | 13.76   | 51   |
| PCBB-2CN-2C8              | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                             | –4.01                  | 4.8 × 10 <sup>–3</sup>                                            | Modifying TiO <sub>2</sub> | 20.68                                  | 1.06                | 79.1   | 17.35   | 53   |

<sup>a</sup> LUMO means the lowest unoccupied molecular orbital energy level. <sup>b</sup> μ is the electron mobility.

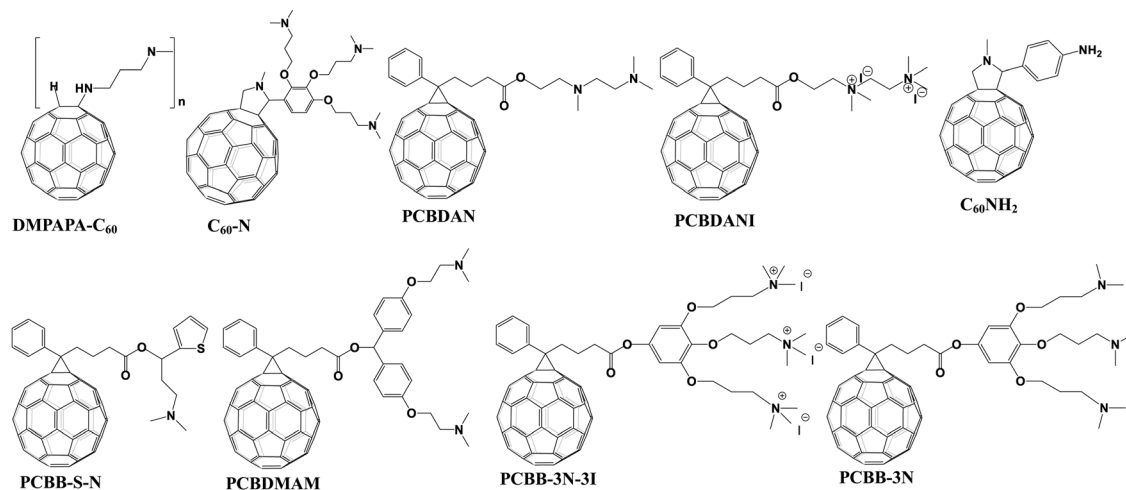
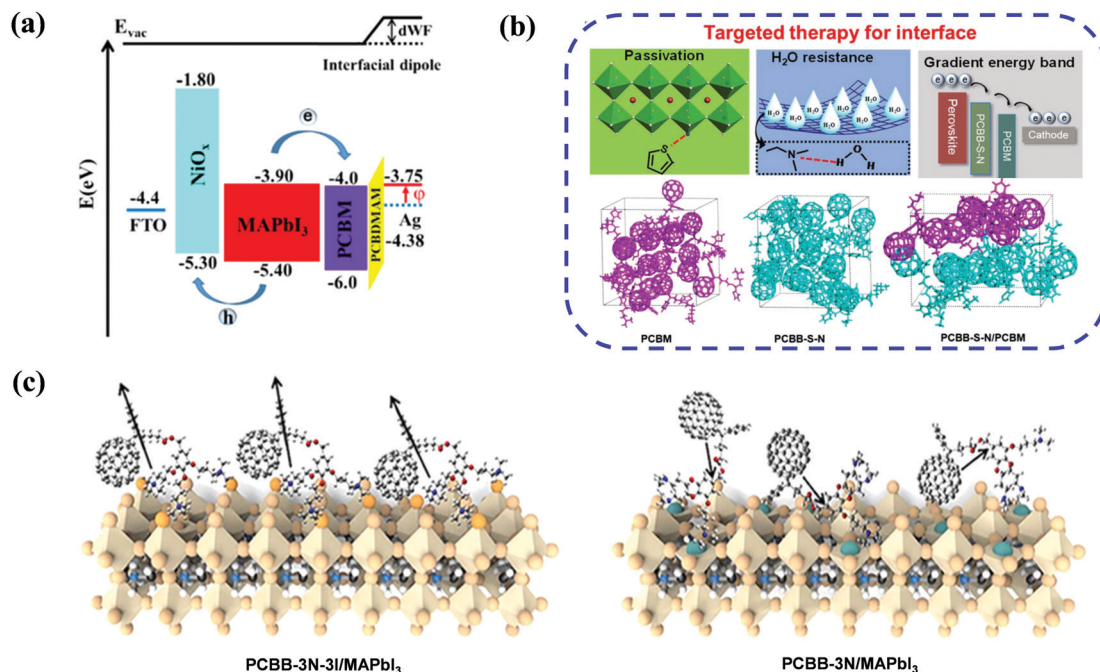


Fig. 4 Molecular structures of amine functionalized fullerene derivatives applied in PSCs.

field and enhancing charge collection.<sup>6,26</sup> In 2015, Azimi *et al.* synthesized a novel dimethylamino-containing fullerene derivative DMAPA-C<sub>60</sub> (Fig. 4) and applied it as a cathode buffer layer (CBL) modifying the PC<sub>61</sub>BM layer of p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> PSCs, achieving a PCE of 13.4% which was higher than that of the control device without the CBL (9.4%). The improved PCE after introducing the DMAPA-C<sub>60</sub> CBL was attributed to the formation of the interfacial dipole layer between PC<sub>61</sub>BM and the Ag electrode. This resulted in the quasi-ohmic contact between the PC<sub>61</sub>BM ETL and the Ag electrode, the reduced work function of the Ag electrode as well as the minimized interfacial energy barrier.<sup>55</sup> Later on, Russell *et al.* reported that incorporating C<sub>60</sub>-N containing three dimethylamino groups (Fig. 4) as an interlayer between the PC<sub>61</sub>BM ETL and the Ag electrode of inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs offered a PCE of 15.5%, which was higher than that of the control device without C<sub>60</sub>-N (7.5%). The incorporated C<sub>60</sub>-N interlayer enabled the lowered work function of the Ag electrode, the reduced combination loss and longer lifetime of free carriers *via* the optimized interface, contributing to the improved device performance.<sup>56</sup> In the same year, Yang *et al.* synthesized another dimethylamino-containing fullerene derivative (PCBDAN, Fig. 4), which was applied as a CBL sandwiched between the PC<sub>61</sub>BM ETL and the Ag electrode in inverted PSCs, affording a PCE of 17.2% with a negligible hysteresis. The PCBDAN interlayer facilitated the decrease of the interface barrier and protected the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite film from the corrosion of moisture.<sup>57</sup> In addition to the application as a CBL, Yang *et al.* further applied PCBDAN as the modification layer of the TiO<sub>2</sub> ETL in planar n-i-p PSCs, achieving improvement of PCE from 13.64% to 16.78% with enhanced light soaking stability. PCBDAN led to a smoother surface and a larger grain size of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite film, a reduced interfacial barrier and a suppressed photocatalytic capability of TiO<sub>2</sub>.<sup>58</sup> One year later, the same group further prepared a self-organized PCBDAN interlayer sandwiched between the ITO electrode and the PC<sub>61</sub>BM ETL, obtaining a PCE of 18.1% with almost free hysteresis and excellent stability maintaining 85% of its initial PCE after 240 h under UV-light soaking. The improved

device performance was attributed to the reduced work function of ITO and minimized interface barriers between the PC<sub>61</sub>BM ETL and the ITO electrode through the self-organized PCBDAN interlayer.<sup>59</sup> Interestingly, PCBDAN can be further ionized by methyl iodide, resulting in a novel methanol-soluble fullerene derivative (PCBDANI, Fig. 4), which was later applied as a CBL in p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> PSCs by Li *et al.* After incorporating the PCBDANI CBL, PSCs exhibited the best PCE of 15.71%, which is attributed to the decreased interfacial recombination derived from the formed interfacial dipole between the PC<sub>61</sub>BM ETL and the Al electrode.<sup>60</sup> Very recently, our group synthesized a novel bis-dimethylamino-functionalized fullerene derivative (PCBDMAM, Fig. 4), which was deposited atop PC<sub>61</sub>BM to construct PC<sub>61</sub>BM/PCBDMAM double fullerene CBLs of p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. The devices based on PC<sub>61</sub>BM/PCBDMAM double fullerene CBLs achieved the highest PCE of 18.11% and enhanced ambient stability, owing to the decreased interfacial energy offset between PC<sub>61</sub>BM and the Ag electrode *via* the reduced work function of the Ag cathode (Fig. 5a).<sup>61</sup>

In addition to the work function modulation of the corresponding metal electrode, amino-functionalized fullerene derivatives can play another important role in defect passivation and interfacial energy band reconstruction. Recently, Xiang *et al.* developed a simple amino-modified fullerene derivative (C<sub>60</sub>NH<sub>2</sub>, Fig. 4) and applied it as an interfacial modifier of the TiO<sub>2</sub> ETL in regular planar PSCs, affording an improved PCE of 18.34% and suppressed hysteresis. The C<sub>60</sub>NH<sub>2</sub> interfacial layer helped to improve crystallinity of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite and the electronic interaction between C<sub>60</sub>NH<sub>2</sub> and the TiO<sub>2</sub> layer, resulting in enhanced photogenerated carrier extraction and reduced interfacial recombination between TiO<sub>2</sub> and the perovskite layer.<sup>62</sup> On the other hand, Li *et al.* synthesized a novel fullerene derivative (PCBB-S-N, Fig. 4) bearing thiophene and amino groups, and applied PCBB-S-N as an intermediary layer atop the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite. The inverted PSCs with a PCBB-S-N interlayer delivered the best PCE of 21.08% and excellent ambient/thermal stability without any encapsulation. Due to the coordination interaction between the thiophene



**Fig. 5** (a) Schematic diagram of iPSCs with a CBL and the cathode interaction process. The energy-level diagram of the iPSCs. Reproduced with permission from ref. 61. Copyright 2020, Elsevier B.V. (b) Functions of PCBB-S-N and three configurations of molecular mutual positions at the end of MD simulation performed under periodic boundary conditions. Reproduced with permission from ref. 63. Copyright 2019, Wiley-VCH. (c) Schematic illustration of the molecular orientation of PCBB-3N-3I and PCBB-3N. Reproduced with permission from ref. 64. Copyright 2019, Nature Publishing Group.

group and  $\text{Pb}^{2+}$  ions as well as the hydrogen bond interaction between the amino moiety and  $\text{H}_2\text{O}$ , the PCBB-S-N interlayer helped to form a compact and homogeneous  $\text{PC}_{61}\text{BM}$  film and regulated the enlarged band energy offset between the perovskite layer and the  $\text{PC}_{61}\text{BM}$  ETL, which is beneficial to enhance the electron transfer capability. Accordingly, they named such interfacial engineering as a targeted therapy strategy (Fig. 5b).<sup>63</sup> Furthermore, in order to eliminate the charged defects at the surface of the organic-inorganic perovskite layer which is detrimental to charge transport, the same group inserted an iodide ionized fullerene derivative (PCBB-3N-3I) between  $\text{PC}_{61}\text{BM}$  and perovskite to construct planar p-i-n  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs, achieving a high PCE of 21.1% and robust ambient stability which was superior to that of the control device (17.70%) and the device with PCBB-3N (15.77%, Fig. 4). PCBB-3N-3I was unveiled to bind the positively charged defects on the perovskite surface *via* electrostatic interaction, which was beneficial for passivating trap states and forming an assembled dipole interlayer atop the perovskite film, leading to an optimized interfacial energy band structure and an extra built-in field for charge collection (Fig. 5c).<sup>64</sup>

### 3.2 Oligoether and crown-ether functionalized fullerene derivatives

In addition to the amino groups, other polar Lewis bases such as oligoether and crown-ether were also used to develop novel fullerene derivatives applied in PSCs. In 2014, Jen *et al.* synthesized a novel fullerene derivative (bis- $\text{C}_{60}$ , Fig. 6) and applied it as an efficient CBL sandwiched between  $\text{PC}_{61}\text{BM}$  and the Ag

electrode in planar p-i-n PSCs. The incorporation of bis- $\text{C}_{60}$  helped to align the energy levels between the  $\text{PC}_{61}\text{BM}$  ETL and the Ag electrode. As a result,  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  PSCs with a bis- $\text{C}_{60}$  interlayer and 1,8-diiodooctane as the auxiliary additive of the perovskite afforded the PCE of 11.8%.<sup>65</sup> In 2018, Li *et al.* used Bis-FIMG and Bis-FITG (Fig. 6) as a CBL atop  $\text{PC}_{61}\text{BM}$  in inverted planar  $\text{CH}_3\text{NH}_3\text{PbI}_3$  p-i-n PSCs, achieving PCEs of 19.31% and 19.01%, respectively, both higher than that of the control device with a BCP CBL (18.8%). Such ionic fullerene derivatives act as surfactants with suitable conductivity, capable of tuning the work function and orthogonal solution-processing.<sup>66</sup>

In 2016, Loi *et al.* prepared a fulleropyrrolidine with a triethylene glycol monoethyl ether side chain (PTEG-1, Fig. 6) and used it as an electron extraction layer (EEL) of planar p-i-n  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  PSCs. Compared to the control device with  $\text{PC}_{61}\text{BM}$  EEL suffering from serious light soaking, the devices based on PTEG-1 EEL exhibited negligible light soaking effect and improved PCE of 15.7%. The superior performance of PTEG-1 EEL was due to its higher dielectric constant (5.9) than that of  $\text{PC}_{61}\text{BM}$  (3.9) and the suppressed trap-assisted recombination resulted from the electron donating side chain groups (Fig. 7a).<sup>67</sup> Likewise, Cao *et al.* synthesized a series of hydrophilic fullerene derivatives bearing electron-rich oligoether chains (Fig. 7b) and applied them as alternative ETLs to replace the  $\text{PC}_{61}\text{BM}$  ETL in inverted planar PSCs. The influences of addition patterns (monoadducts or bisadduct), the number of oligoether chains and the type of fullerenes ( $\text{C}_{60}$  and  $\text{C}_{70}$ ) on the ETL performance were elucidated, and PSCs based on  $\text{C}_{70}$ -DPM-OE

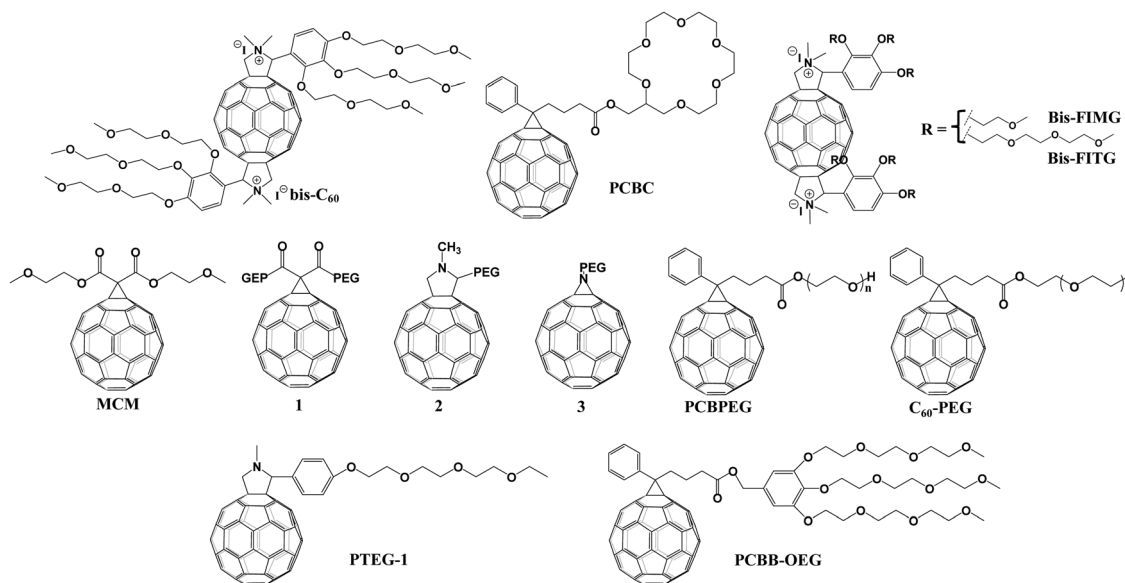


Fig. 6 Molecular structures of oligoether and crown-ether functionalized fullerene derivatives applied in PSCs.

with the optimized molecular structures exhibited the highest PCE of 16%. The electron-rich oligoether chains within  $C_{70}$ -DPM-OE enable the enhanced interfacial charge transport efficiency, the modified work function of Ag cathodes and the passivated trap states at the  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  perovskite surface.<sup>68</sup> In 2012, two novel fullerene derivatives including MCM bearing an oligoether group (Fig. 6) and PCP bearing a pyridine moiety (Fig. 8) were synthesized *via* Bingel reactions and applied as ETLs in thick-film  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs (absorber layer > 1  $\mu\text{m}$ ) by Li *et al.*, affording a PCE of 19.11% and 19.32%, respectively. Comparing these two ETMs, the authors proposed that the subtle intermolecular interaction (anion- $\pi$  and Lewis acid-base) between the ETL and the perovskite determines the carrier extraction and transport at the interface between the perovskite and the cathode, which are

correlated to the device hysteresis and performance. Furthermore, this study points out that the stronger coordination interaction of the N atom and  $\text{Pb}^{2+}$  ( $\text{N-Pb}^{2+}$ ) than that of  $\text{O-Pb}^{2+}$  results in serious hysteresis owing to the energetic misalignment as well as the charge accumulation at the perovskite/PCP heterojunction.<sup>69</sup>

In 2018, Li *et al.* grafted tri-hydrophilic OEG chains onto the fullerene cage and applied the as-synthesized PCBB-OEG (Fig. 6) as an additive in the MAI precursor solution to prepare p-i-n planar PSCs by the two-step deposition method.<sup>70</sup> PCBB-OEG in the MAI solution acts as a soft-template to assist the growth of high-quality  $\text{CH}_3\text{NH}_3\text{PbI}_3$  crystals through diffusion into the pre-deposited  $\text{PbI}_2$ :MAI film, resulting in a top-down gradient distribution of the fullerene derivative in the perovskite film, which is beneficial for improving electronic coupling

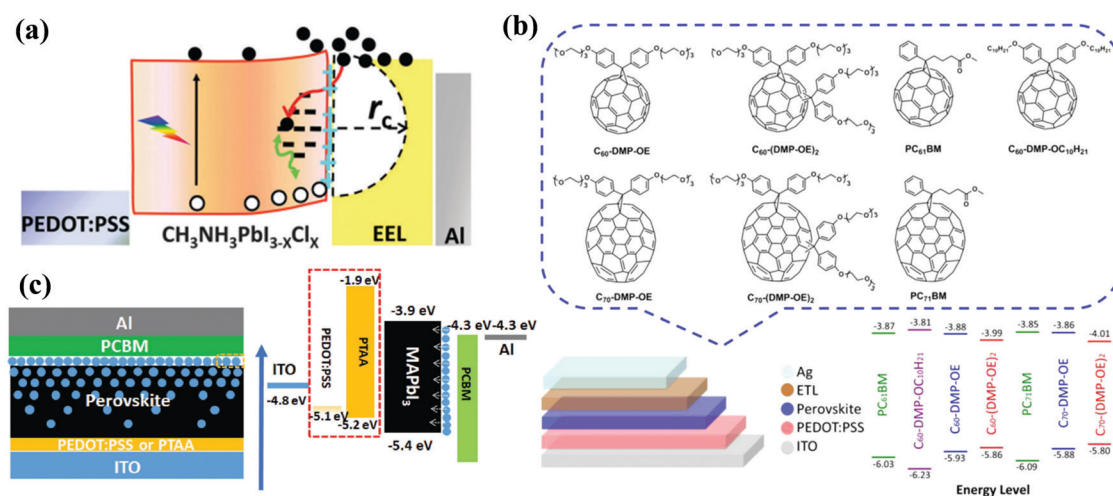


Fig. 7 (a) Proposed mechanism for the light-soaking effect for the device with  $\text{PC}_{61}\text{BM}$  and PTEG-1. Reproduced with permission from ref. 67. Copyright 2016, Royal Society of Chemistry. (b) Chemical structure of fullerene derivatives and the corresponding energy-level diagram. Reproduced with permission from ref. 68. Copyright 2016, Elsevier Ltd. (c) Device configuration and the corresponding energy-level diagram of the PSCs. Reproduced with permission from ref. 70. Copyright 2018, Wiley-VCH.

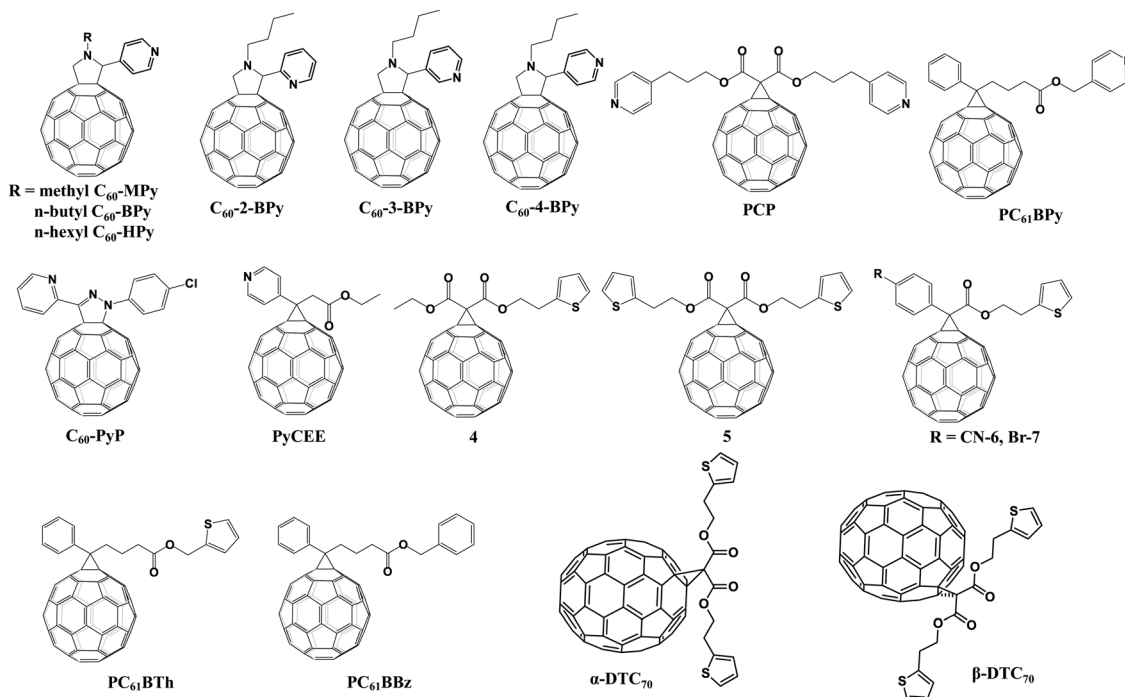


Fig. 8 Molecular structures of heterocyclic functionalized fullerene derivatives applied in PSCs.

and band alignment at the interface and reducing the trap-states at the perovskite grain boundaries (Fig. 7c). These advantages contribute to an enhanced PCE of 20.2% for a rigid device on a glass substrate and a PCE of 18.1% for the flexible PSCs without hysteresis. Besides, the anchoring of PCBB-OEG with perovskite *via* the hydrogen bond interaction between  $-O$  of  $-OEG$  and  $-NH_3$  of MA, as well as the outside orientation of  $C_{60}$  moieties at the perovskite surface, simultaneously contribute to the enhancements of the stability of the perovskite crystal lattice and water resistance. As a result, PSCs with the PCBB-OEG additive demonstrate an outstanding ambient stability maintaining more than 98.4% of the initial PCE after storing the device under  $\approx 50$ –70% RH after 300 h without any encapsulation. In 2019, the same group further carried out an in-depth investigation of the mechanism toward the oxygen-stabilizing effect of PCBB-OEG doping both in the perovskite active layer and in the  $PC_{61}BM$  ETL.<sup>71</sup> The PCBB-OEG additive in the perovskite and the  $PC_{61}BM$  ETL enhanced electron extraction and transport capability from  $CH_3NH_3PbI_3$  to the PCBB-OEG/ $PC_{61}BM$  layer, preventing the formation of  $O_2^{\bullet-}$  from the photogenerated charge reaction with oxygen which is responsible for device degradation.<sup>71</sup>

In 2015, Li *et al.* reported a new alcohol-soluble crown-ether-containing fullerene derivative (PCBC, Fig. 6) and applied it as a CBL between  $PC_{61}BM$  and the Al electrode in inverted planar  $CH_3NH_3PbI_{3-x}Cl_x$  PSCs. The incorporated PCBC CBL improved the interfacial Ohmic contact between  $PC_{61}BM$  and Al and lowered the interfacial resistance, which is beneficial for electron extraction and transport, resulting in an improved PCE of 15.08%.<sup>72</sup> Soon after, Li *et al.* deposited a LiF interlayer atop of PCBC to construct the PCBC/LiF double CBL of planar p-i-n

$CH_3NH_3PbI_{3-x}Cl_x$  PSCs, affording a PCE of 15.53%, which is higher than that of the control device with only LiF CBL (13.54%). Furthermore, the devices with the PCBC/LiF double CBL demonstrate superior long-term stability to that of the control device with a LiF single CBL. The enhanced performance is attributed to the reduced series resistance ( $R_s$ ) from the better Ohmic contact between  $PC_{61}BM$  and the LiF/Al electrode induced by the dipole moment of PCBC.<sup>73</sup>

In 2018, Delgado *et al.* presented three kinds of poly(ethylene glycol) (PEG) functionalized fullerene derivatives (1, 2, 3, Fig. 6) and incorporated them as additives in the  $CH_3NH_3PbI_3$  perovskite layer of regular PSCs, showing a suppressed hysteresis and increased moisture stability. They found that increasing the number of PEG moieties led to the enhanced device stability, and it was interpreted that the increased hygroscopicity of PEG chains was beneficial for retaining water, thus preventing the perovskite from degrading.<sup>74</sup> Similarly, Wu *et al.* developed two PEG end-capped fullerene derivatives (PCBPEG-4k and PCBPEG-20k, Fig. 6) and applied them as additives in the  $CH_3NH_3PbI_3$  perovskite layer of planar regular PSCs, affording a PCE of 17.72% and 17.36%, respectively. Incorporating PCBPEG-4k and PCBPEG-20k additives into the perovskite layer improved the perovskite morphology and photovoltaic performance of the device, which is due to the enlarged crystal grain size, reduced defect density and improved charge transfer properties.<sup>75</sup> Later on, Hu *et al.* reported another similar PEG end-capped fullerene derivative ( $C_{60}$ -PEG, Fig. 6), which was incorporated as an additive into the  $CS_{0.1}FA_{0.7}MA_{0.2}I_{3-x}Br_x$  perovskite layer in planar inverted PSCs *via* the anti-solvent process. The incorporation of  $C_{60}$ -PEG enlarges the perovskite crystal size and passivates the defects of the perovskite film, leading to higher electron mobility and

lower carrier recombination as well as the increased PCE of 17.71%.<sup>76</sup>

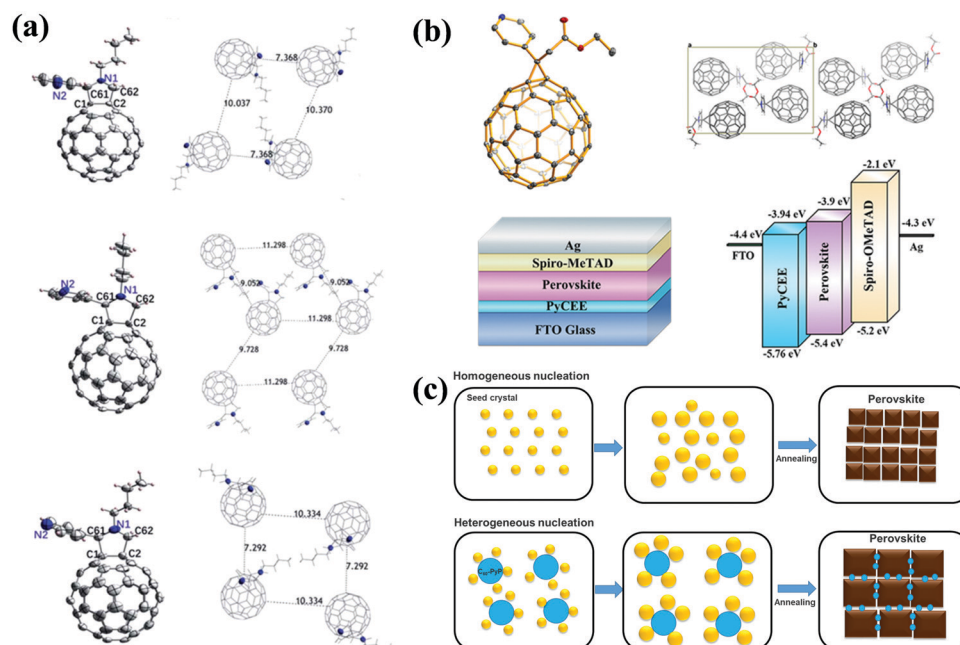
### 3.3 Heterocyclic pyridine and thiophene functionalized fullerene derivatives

Pyridine and thiophene are two representative heterocyclic groups and common Lewis bases which are used to regulate the crystallization of perovskite and passivate the trap states through the strong coordination interactions between  $\text{Pb}^{2+}$  ions and nitrogen/sulfur atoms bearing lone pair electrons.<sup>77</sup> In 2019, our group first grafted the pyridine group onto  $\text{C}_{60}$  and synthesized three novel pyridine-functionalized fullerene derivatives with different alkyl groups (methyl, *n*-butyl, and *n*-hexyl, abbreviated as  $\text{C}_{60}$ -MPy,  $\text{C}_{60}$ -BPy, and  $\text{C}_{60}$ -HPy respectively, Fig. 8) *via* a one-step 1,3-dipolar cycloaddition reaction (*i.e.*, Prato reaction), and applied them as ETLs in p-i-n PSCs.<sup>78</sup> The pyridine moiety within  $\text{C}_{60}$ -Py can coordinate with  $\text{Pb}^{2+}$  ions of  $\text{CH}_3\text{NH}_3\text{PbI}_3$  to passivate the trap states and suppress the nonradioactive recombination, leading to the improved electron transfer and device performance. The PCE based on the  $\text{C}_{60}$ -BPy ETL demonstrated the highest PCE of 16.83%, which is higher than that of the control device based on the  $\text{PC}_{61}\text{BM}$  ETL (15.87%). In addition, the longest *N*-alkyl group could act as an encapsulating layer protecting the perovskite film from the erosion of moisture, thus improving the ambient stability of PSC devices.<sup>78</sup> Furthermore, very recently we carried out a follow-up study on the effect of the nitrogen site on the ETL performance of  $\text{C}_{60}$ -BPy based on syntheses of three pyridine-functionalized fullerene derivatives with different nitrogen sites abbreviated as  $\text{C}_{60}$ -*n*-Py (*n* = 2, 3, 4, Fig. 8). Interestingly, after incorporating  $\text{C}_{60}$ -*n*-Py as ETLs in

p-i-n PSCs, it was found that  $\text{C}_{60}$ -3-Py with the optimal nitrogen site fulfilled the strongest coordination interactions with  $\text{Pb}^{2+}$  ions and consequently passivated the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite defects at the most. As a result,  $\text{C}_{60}$ -3-Py-based PSC devices achieved the highest PCE of 17.57% (Fig. 9a).<sup>79</sup>

Another pyridine-functionalized fullerene derivative PCP (Fig. 8) was synthesized by Li *et al.* *via* the Bingel reaction and applied as the ETL in p-i-n PSCs, leading to an improved PCE of 19.32%.<sup>69</sup> In 2019, Deng and Xie *et al.* synthesized a novel pyridine-functionalized fullerene derivative (PyCEE, Fig. 8) and applied it as an alternative of the traditional  $\text{TiO}_2$  ETL to construct planar n-i-p PSCs. Compared with  $\text{TiO}_2$ , the PyCEE ETL possesses a poor-wetting surface, more suitable energy levels, higher electron mobility and stronger trap passivation capability by the coordination interactions with  $\text{Pb}^{2+}$  within the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  film, leading to large-sized perovskite films, higher electron extraction/transport ability, suppressed hysteresis and the champion PCE of 18.27% (Fig. 9b).<sup>80</sup>

A series of thiophene-grafted fullerene derivatives (4–7, Fig. 8) were synthesized by Bingel reactions and applied as novel ETLs in inverted  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs by Echegoyen and co-workers. Compared with  $\text{PC}_{61}\text{BM}$  ETLs, PSCs with these new thiophene-grafted fullerene derivative ETLs exhibited improved PCE, owing to the passivation of the defects of the perovskite surface by the coordination interactions between Pb and S atoms. Interestingly, among the three fullerene derivatives, devices based on fullerene derivatives bearing highly polar –CN groups exhibited the highest PCE of 17.77% due to the increased dielectric constant ( $\epsilon_r$ ), which could decrease the recombination ratio and facilitate the charge transfer.<sup>81</sup> More recently, the same group prepared



**Fig. 9** (a) Crystal structure and the corresponding molecular packing of  $\text{C}_{60}$ -*n*-Py (*n* = 2, 3, 4). Reproduced with permission from ref. 79. Copyright 2020, Royal Society of Chemistry. (b) Crystal structure, the corresponding molecular packing of PyCEE, and the energy-level diagram of the PSCs. Reproduced with permission from ref. 80. Copyright 2019, American Chemical Society. (c) Schematic illustration of the perovskite nucleation process without and with  $\text{C}_{60}$ -PyP. Reproduced with permission from ref. 27. Copyright 2019, Royal Society of Chemistry.

another thiophene-grafted fullerene derivative PC<sub>61</sub>BTh and compared its performance with the analogous derivatives PC<sub>61</sub>BBz and PC<sub>61</sub>BPy (Fig. 8) bearing, respectively, benzyl and pyridine as the end groups so as to investigate the influence of the heterocyclic groups on the photovoltaic performance and interfacial interactions. Among them, PC<sub>61</sub>BPy with a pyridine group exhibited the strongest interfacial interactions with Pb<sup>2+</sup> ions of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite surface, which leads to more effective trap passivation and decreased electron/hole recombination, and consequently the best PCE of 17.84%.<sup>82</sup> Very recently, they further synthesized two new thiophene substituted C<sub>70</sub> isomers,  $\alpha$  and  $\beta$  bis(2-(thiophen-2-yl)ethyl)-C<sub>70</sub>-fullerene monoadducts ( $\alpha$ -DTC<sub>70</sub> and  $\beta$ -DTC<sub>70</sub>, Fig. 8), which were applied as ETLs in inverted CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. They found that, compared with the original fullerene,

the change in the orientation of fullerene is due to the carbonyl-lead interaction that fixes the fullerene on the surface of the perovskite, and the shortest contacts between  $\alpha$ -DTC<sub>70</sub> and the perovskite afforded an improved electron extraction ability, leading to improved  $J_{sc}$  and FF of the devices with a PCE of 15.9%, which is higher than those of the traditional PC<sub>71</sub>BM ETL (15.1%) and  $\beta$ -DTC<sub>70</sub> ETL (8.80%).<sup>83</sup>

In addition to the applications as ETLs in PSCs, incorporating these heterocyclic pyridine and thiophene fullerene derivatives into the perovskite layer as additives to construct BHJ-PSCs is another effective way to improve device performance. In 2019, our group synthesized a pyridine-functionalized fullerene derivative (C<sub>60</sub>-PyP, Fig. 8) and applied it as an additive of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite film in p-i-n PSCs. The incorporation of C<sub>60</sub>-PyP additives into the perovskite led to lowering of the

**Table 2** Device performance of PSCs incorporating amine, oligoether and crown-ether functionalized fullerene derivatives

| Compound                                               | Active layer                                                                           | LUMO (eV) | $\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ) | Role of the molecule       | $J_{sc}$ (mA cm <sup>-2</sup> ) | $V_{oc}$ (V) | FF (%) | PCE (%) | Ref. |
|--------------------------------------------------------|----------------------------------------------------------------------------------------|-----------|----------------------------------------------------------|----------------------------|---------------------------------|--------------|--------|---------|------|
| DMPAPA-C <sub>60</sub>                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | —         | —                                                        | CBL                        | 17.90                           | 0.97         | 77     | 13.40   | 55   |
| C <sub>60</sub> -N                                     | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.9      | —                                                        | CBL                        | 20.50                           | 1.03         | 74     | 15.50   | 56   |
| PCBDAN                                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -4.1      | —                                                        | CBL                        | 20.71                           | 1.08         | 77.00  | 17.20   | 57   |
| PCBDAN                                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -4.1      | —                                                        | Modifying TiO <sub>2</sub> | 21.3                            | 1.05         | 75.05  | 16.78   | 58   |
| PCBDAN                                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -4.1      | —                                                        | Interfacial layer          | 21.70                           | 1.08         | 77.3   | 18.1    | 59   |
| PCBDANI                                                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -3.68     | —                                                        | CBL                        | 21.28                           | 0.91         | 81.00  | 15.71   | 60   |
| PCBDMAM                                                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | —         | 1.08 × 10 <sup>-4</sup>                                  | CBL                        | 22.20                           | 1.034        | 78.87  | 18.11   | 61   |
| C <sub>60</sub> NH <sub>2</sub>                        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | —         | —                                                        | Modifying TiO <sub>2</sub> | 22.52                           | 1.07         | 77     | 18.34   | 62   |
| PCBB-S-N                                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -4.0      | 3.37 × 10 <sup>-4</sup>                                  | Intermediary layer         | 23.83                           | 1.12         | 79.09  | 21.08   | 63   |
| PCBB-3N                                                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.62     | 2.90 × 10 <sup>-4</sup>                                  | Intermediary layer         | 21.05                           | 1.046        | 71.65  | 15.77   | 64   |
| PCBB-3N-3I                                             | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.66     | 9.24 × 10 <sup>-4</sup>                                  | Intermediary layer         | 23.46                           | 1.105        | 81.36  | 21.10   | 64   |
| Bis-C <sub>60</sub>                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | —         | —                                                        | CBL                        | 17.5                            | 0.92         | 73     | 11.8    | 65   |
| Bis-FIMG                                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.97     | —                                                        | CBL                        | 22.92                           | 1.08         | 79.5   | 19.31   | 66   |
| Bis-FITG                                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.99     | —                                                        | CBL                        | 22.15                           | 1.07         | 80.4   | 19.01   | 66   |
| PCBC                                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | —         | —                                                        | CBL                        | 22.08                           | 0.98         | 70     | 15.08   | 72   |
| PCBC                                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | —         | —                                                        | CBL                        | 21.54                           | 1.00         | 72.5   | 15.53   | 73   |
| PTEG-1                                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | —         | —                                                        | ETL                        | 20.63                           | 0.94         | 81     | 15.71   | 67   |
| C <sub>60</sub> -DMP-OE                                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -3.88     | 5.0 × 10 <sup>-4</sup>                                   | ETL                        | 21.4                            | 0.96         | 76     | 15.5    | 68   |
| C <sub>60</sub> -(DMP-OE) <sub>2</sub>                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -3.99     | 1.8 × 10 <sup>-5</sup>                                   | ETL                        | 20.7                            | 0.93         | 71     | 13.8    | 68   |
| C <sub>60</sub> -DMP-OCH <sub>10</sub> H <sub>21</sub> | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -3.81     | 1.1 × 10 <sup>-4</sup>                                   | ETL                        | 19.9                            | 0.90         | 60     | 10.8    | 68   |
| C <sub>70</sub> -DMP-OE                                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -3.86     | 3.3 × 10 <sup>-4</sup>                                   | ETL                        | 21.9                            | 0.97         | 75     | 16.0    | 68   |
| C <sub>70</sub> -(DMP-OE) <sub>2</sub>                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                     | -4.01     | 1.7 × 10 <sup>-5</sup>                                   | ETL                        | 21.0                            | 0.94         | 71     | 14.0    | 68   |
| MCM                                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | —                                                        | ETL                        | 22.12                           | 1.08         | 80     | 19.11   | 69   |
| 1                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.72     | —                                                        | Additive                   | 20.7                            | 1.09         | 73     | 16.41   | 74   |
| 2                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.64     | —                                                        | Additive                   | 17.8                            | 1.06         | 76     | 15.07   | 74   |
| 3                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.69     | —                                                        | Additive                   | 18.5                            | 1.07         | 78     | 16.37   | 74   |
| PCBPEG-4k                                              | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | —         | —                                                        | Additive                   | 21.28                           | 1.073        | 77.62  | 17.72   | 75   |
| PCBPEG-20k                                             | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | —         | —                                                        | Additive                   | 21.21                           | 1.074        | 76.17  | 17.36   | 75   |
| C <sub>60</sub> -PEG                                   | CS <sub>0.1</sub> FA <sub>0.7</sub> MA <sub>0.2</sub> I <sub>3-x</sub> Br <sub>x</sub> | —         | —                                                        | Additive                   | 20.50                           | 1.04         | 81.66  | 17.41   | 76   |
| PCBB-OEG                                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | —         | —                                                        | Additive                   | 23.65                           | 1.07         | 80     | 20.2    | 70   |
| C <sub>60</sub> -MPy                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.80     | 1.97 × 10 <sup>-3</sup>                                  | ETL                        | 20.2                            | 1.016        | 78.4   | 16.1    | 78   |
| C <sub>60</sub> -Bpy                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.81     | 3.51 × 10 <sup>-3</sup>                                  | ETL                        | 22.8                            | 1.003        | 74.2   | 16.8    | 78   |
| C <sub>60</sub> -HPy                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.83     | 1.04 × 10 <sup>-3</sup>                                  | ETL                        | 20.6                            | 0.988        | 70.8   | 14.4    | 78   |
| C <sub>60</sub> -2-BPy                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.78     | 1.02 × 10 <sup>-3</sup>                                  | ETL                        | 20.45                           | 0.85         | 64.67  | 12.68   | 79   |
| C <sub>60</sub> -3-Bpy                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.80     | 2.95 × 10 <sup>-3</sup>                                  | ETL                        | 22.46                           | 1.02         | 76.42  | 17.57   | 79   |
| C <sub>60</sub> -4-BPy                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.81     | 2.64 × 10 <sup>-3</sup>                                  | ETL                        | 22.85                           | 1.00         | 74.20  | 16.83   | 79   |
| PCP                                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | —                                                        | ETL                        | 22.31                           | 1.11         | 78     | 19.32   | 69   |
| PyCEE                                                  | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.94     | —                                                        | ETL                        | 22.95                           | 1.05         | 75.83  | 18.27   | 80   |
| 4                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | 1.32 × 10 <sup>-3</sup>                                  | ETL                        | 21.00                           | 0.93         | 82     | 16.01   | 81   |
| 5                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | 4.58 × 10 <sup>-3</sup>                                  | ETL                        | 22.10                           | 0.94         | 83     | 17.22   | 81   |
| 6                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | 7.68 × 10 <sup>-3</sup>                                  | ETL                        | 22.30                           | 0.96         | 83     | 17.77   | 81   |
| 7                                                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.86     | 6.21 × 10 <sup>-3</sup>                                  | ETL                        | 22.10                           | 0.92         | 84     | 17.08   | 81   |
| PC <sub>61</sub> BBz                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.80     | 3.70 × 10 <sup>-4</sup>                                  | ETL                        | 24.33                           | 0.999        | 69     | 16.57   | 82   |
| PC <sub>61</sub> BTh                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.72     | 3.65 × 10 <sup>-4</sup>                                  | ETL                        | 24.12                           | 0.950        | 68     | 15.74   | 82   |
| PC <sub>61</sub> BPy                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.71     | 3.66 × 10 <sup>-4</sup>                                  | ETL                        | 24.85                           | 0.966        | 74     | 17.46   | 82   |
| $\alpha$ -DTC <sub>70</sub>                            | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.88     | 3.68 × 10 <sup>-3</sup>                                  | ETL                        | 22.00                           | 0.874        | 82.6   | 15.9    | 83   |
| $\beta$ -DTC <sub>70</sub>                             | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.87     | 3.51 × 10 <sup>-3</sup>                                  | ETL                        | 14.09                           | 0.812        | 76.9   | 8.80    | 83   |
| C <sub>60</sub> -PyP                                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                       | -3.89     | —                                                        | Additive                   | 22.31                           | 1.09         | 78.26  | 19.82   | 27   |

nucleation Gibbs free energy and controlled crystalline orientation, resulting in improved crystallinity and reduced trap states (Fig. 9c) through the coordination interaction between the N atom of the pyridine and  $\text{Pb}^{2+}$  ions. As a result, the best PCE reached up to 19.82%, which is dramatically higher than that of the control devices without an additive (17.61%).<sup>27</sup>

All of the above-mentioned Lewis base functionalized fullerene derivatives and their corresponding photovoltaic parameters are summarized in Table 2. Comparing these results, it is found that fullerene derivatives functionalized by amino, oligoether, and crown ether groups are mainly used as CBLs of PSCs sandwiched between ETLs and metal electrodes, which helps to form an interfacial dipole layer for reducing the work function of the metal cathode and promoting the electron transport. The heterocyclic pyridine and thiophene groups bearing the lone pair electrons on N and S atoms respectively can enable the coordination interactions with  $\text{Pb}^{2+}$  ions of perovskite, leading to an effective passivation of the trap states and promoted charge transport. Therefore, Lewis base functionalized fullerene derivatives are now in the developmental stages and have great potential in boosting the performance of PSCs.

## 4. Carboxyl and hydroxyl functionalized fullerene derivatives

### 4.1 Carboxyl functionalized fullerene derivatives

To date,  $\text{TiO}_2$  and  $\text{SnO}_2$  are two most commonly used ETL materials in planar n-i-p PSCs. However, the oxygen vacancy-related defects at the surface of  $\text{TiO}_2$  and  $\text{SnO}_2$  ETLs are a notorious charge capture center to deteriorate the electronic properties, leading to poor charge transport as well as serious trap-assistant recombination.<sup>84</sup> To address these issues, in 2013, Snaith and co-workers used a self-assembled monolayer (SAM) of a carboxyl ( $-\text{COOH}$ )-functionalized fullerene derivative ( $\text{C}_{60}\text{SAM}$ ) to modify the mesoporous  $\text{TiO}_2$  ETL (Fig. 10).  $\text{C}_{60}\text{SAM}$  acted as an electron acceptor and inhibited electron transfer from the perovskite to  $\text{TiO}_2$ , resulting in a decrease in energy loss within mesoporous n-i-p PSCs.<sup>85</sup> In a follow-up study, the same group further inserted  $\text{C}_{60}\text{SAM}$  between the perovskite and  $\text{TiO}_2$  to construct planar n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  PSCs, achieving the champion PCE of 17.3% with reduced hysteresis (Fig. 11a).  $\text{C}_{60}\text{SAM}$  incorporation is beneficial for the reduced trap states at the surface and the suppressed nonradiative recombination through the anchoring group of  $\text{C}_{60}\text{SAM}$ .<sup>86</sup> In 2016, Mora-Sero *et al.* presented three different fullerene derivatives (Fig. 10) functionalized with carboxyl and cyanide groups, which were used as SAMs at the electron selective contact-perovskite interface, leading to a PCE of 13.5% with remarkable reduced  $J-V$  hysteresis. The grafted carboxyl and cyanide groups within fullerene derivatives could anchor onto the  $\text{TiO}_2$  surface and the  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  perovskite film, respectively, leading to a reduction in capacitive hysteresis observed for oxide-based anodes in PSCs.<sup>87</sup> In the same year, Huang *et al.* used  $\text{C}_{60}\text{SAM}$  and trichloro(3,3,3-trifluoropropyl)

silane to construct a hydrophobic cross-linkable fullerene ETL via the hydrogen bond interaction between the  $-\text{COOH}$  of  $\text{C}_{60}\text{SAM}$  and the  $-\text{OH}$  of the silane coupling molecule as well as the Si-O crosslink bonding. The cross-linkable fullerene ETL could block any accessible pathways of water molecule permeation into  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite grain boundaries and protect the underneath perovskite films from moisture-caused erosion (Fig. 11b). Although the cross-linkable fullerene ETL improves the transport properties of the ETL, further doping of a small amount of MAI as an n-type dopant into a fullerene derivative leads to a dramatically increased conductivity of the ETL by over 100-fold. The simultaneous contributions of enhanced conductivity and water-resistance of the ETL led to an improved PCE of 19.5% in the planar p-i-n PSCs and an outstanding moisture stability of the device, retaining more than 90% of its initial PCE after 30 days of storage in air.<sup>88</sup> Likewise, Bo *et al.* applied a simpler carboxyl functionalized fullerene derivative PCBA (Fig. 10) to modify the compact  $\text{TiO}_2$  ETL in planar n-i-p PSCs, obtaining a PCE of 17.76% and a  $V_{\text{oc}}$  of 1.16 V under reverse scanning. PCBA played two important roles in blocking the holes and passivating the trap states on the  $\text{TiO}_2$  surface, leading to a reduced charge carrier recombination at the  $\text{TiO}_2/\text{CH}_3\text{NH}_3\text{PbI}_3$  interface and improving the morphology of the perovskite film.<sup>89</sup>

Multi-adducts of carboxyl functionalized fullerene derivatives were also used in PSCs. In 2015, Gong *et al.* synthesized a novel multi-adduct water/alcohol soluble carboxyl functionalized fullerene derivative ( $\text{A}_{10}\text{C}_{60}$ ) bearing ten carboxyl groups and incorporated it into the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  active layer as an additive to fabricate BHJ-PSCs (Fig. 10). The incorporated  $\text{A}_{10}\text{C}_{60}$  (9.6% w/w) in PSCs helped to balance the carrier extraction efficiency and enlarge the interface between the perovskite and  $\text{A}_{10}\text{C}_{60}$ , leading to an improved PCE of 13.97% relative to that of the control device (11.75%).<sup>90</sup> In another study, the same group used  $\text{A}_{10}\text{C}_{60}$  to re-engineer the  $\text{PC}_{61}\text{BM}$  ETL surface to address the poor wettability of  $\text{PbI}_2$  atop of the  $\text{PC}_{61}\text{BM}$  layer and to block the hole back transfer into the cathode. As a result, the planar n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs with  $\text{A}_{10}\text{C}_{60}$  interfacial layers exhibited a PCE of 14.6%.<sup>91</sup>

In 2017, Fang *et al.* synthesized a novel carboxyl functionalized fullerene derivative named as  $\text{C}_{60}$  pyrrolidine tris-acid (CPTA, Fig. 10) and applied it as an independent ETL to replace the traditional metal oxide ETLs in n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs, achieving decent PCEs of 18.39% and 17.04% for the glass substrate and the flexible device, respectively. The advantages of the CPTA ETL including outstanding electron mobility, appropriate energy levels, and conformal architecture by covalently anchoring onto the surface of ITO via the carboxyl groups are helpful to eliminate photocurrent hysteresis (Fig. 11c) and enhance the long-term stability of devices.<sup>92</sup> In addition, CPTA was also widely used as a modification layer of the traditional metal oxide ETLs in n-i-p PSCs. In 2019, Xu *et al.* utilized CPTA to modify the  $\text{SnO}_2$  ETL in flexible n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs, achieving a PCE of 18.36% and good stability, retaining 87% of its initial PCE after 46 days of exposure to 30% relative humidity at 25 °C without any

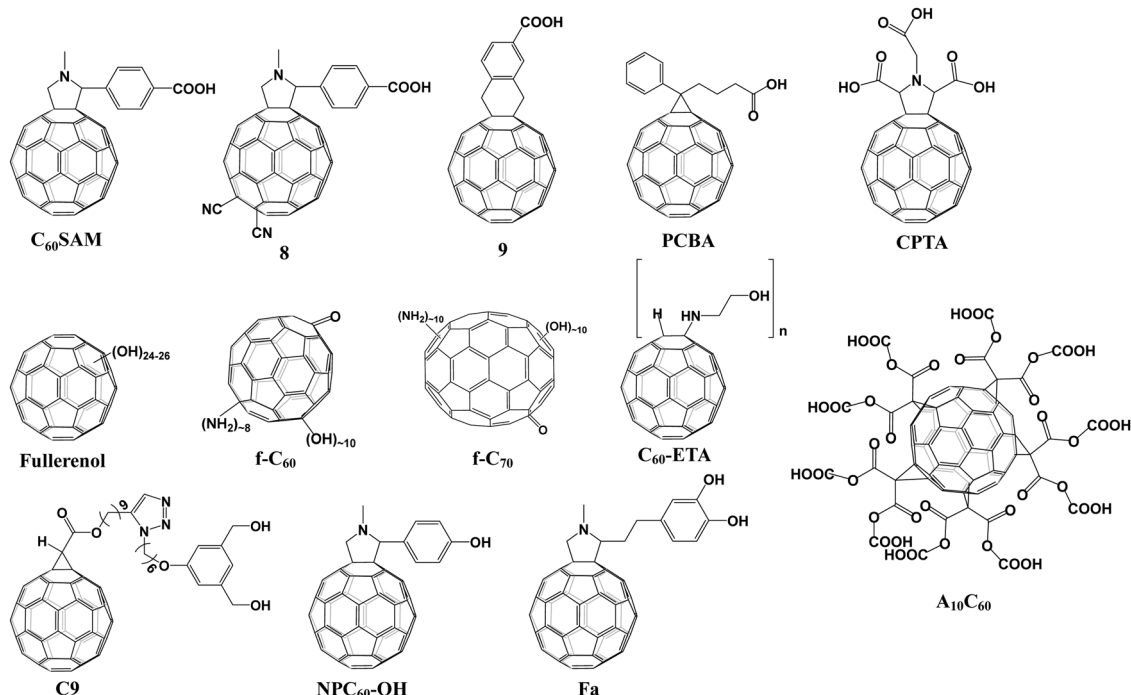


Fig. 10 Molecular structures of carboxyl and hydroxyl functionalized fullerene derivatives applied in PSCs.

encapsulation.<sup>93</sup> In their subsequent study, CPTA was further extended to modify the  $\text{SnO}_2$  ETL for constructing planar n-i-p PSCs based on the  $\text{FASnI}_3$  light-absorbing layer, leading to a PCE of 7.40% and the record  $V_{oc}$  of 0.72 V.<sup>94</sup>

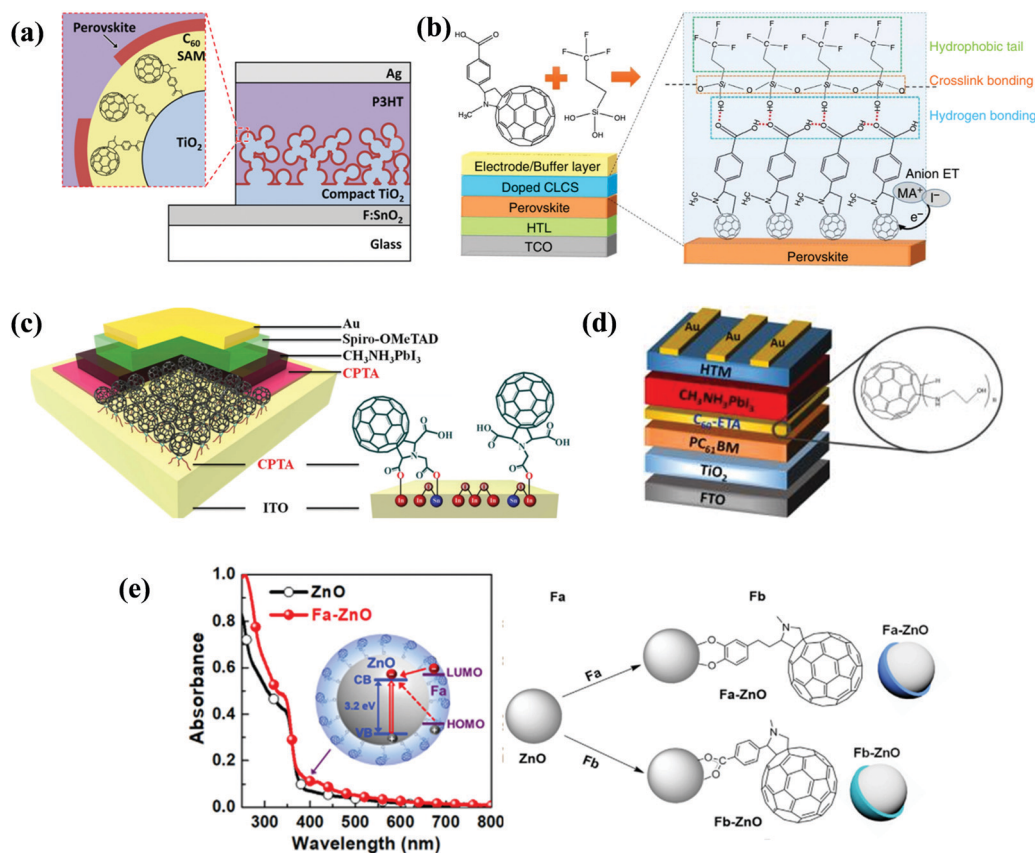
Based on these reports, the carboxyl groups grafted onto fullerene have two distinct features, such as the high molecular polarity and the anchoring ability with metal oxide ETLs. Therefore, carboxyl functionalized fullerene derivatives have versatile functions including modifying metal oxide ETLs, additives of perovskite layers, ETLs and interfacial layers in PSCs.

#### 4.2 Hydroxyl functionalized fullerene derivatives

A hydroxyl ( $-\text{OH}$ ) group is another representative polar group possessing the anchoring function with metal oxides similar to the carboxyl group. In 2016, a water-soluble fullerene derivative (fullerenol) with multiple hydroxyl groups (Fig. 10) was first used by Chen *et al.* to modify the  $\text{TiO}_2$  ETL in n-i-p PSCs. The fullerenol with excellent conductivity sandwiched between  $\text{TiO}_2$  and the  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  perovskite layer is beneficial for the electron transport and surface wettability of  $\text{TiO}_2$ , leading to a reduced interfacial resistance and increased crystallinity of the perovskite film. Furthermore, inserting fullerenol into PSCs helps to obtain matched energy level alignments between the perovskite and the cathode. As a result, the PSC devices with fullerenol ETLs deliver the PCE of 14.69%.<sup>95</sup> Later on, the same group further developed two water-soluble fullerene derivatives f- $\text{C}_{60}$  and f- $\text{C}_{70}$  (Fig. 10) bearing three types of functional groups including  $-\text{OH}$ ,  $-\text{NH}_2$  and  $-\text{C}=\text{O}$ , and applied them as the buffer layer sandwiched between the  $\text{C}_{60}$  ETL and the ITO electrode to construct planar n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  PSCs. The PSC devices with a f- $\text{C}_{60}$  interlayer afford the champion

PCE of 16.97%, which is higher than that of the PSCs with the f- $\text{C}_{70}$  interlayer. This is attributed to the higher symmetry of the  $\text{C}_{60}$  cage than that of f- $\text{C}_{70}$ , leading to more even distribution of the functional groups on the fullerene cage and improved energy band alignment.<sup>96</sup> In addition, our group utilized a novel ethanolamine (ETA)-functionalized fullerene derivative  $\text{C}_{60}$ -ETA (Fig. 10) and  $\text{PC}_{61}\text{BM}$  to successively modify  $\text{TiO}_2$  ETLs in planar n-i-p PSCs. The devices based on double fullerene modification layers resulted in an improved PCE of 18.49%, which was higher than that of the single  $\text{PC}_{61}\text{BM}$  or  $\text{C}_{60}$ -ETA modification layer. This was attributed to the defect passivation of the  $\text{TiO}_2$  surface by  $\text{PC}_{61}\text{BM}$ , the improved wettability of the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite film on the ETL and more efficient charge transfer between the perovskite and the  $\text{TiO}_2$  ETL (Fig. 11d).<sup>97</sup>

In 2018, a hydrophobic fullerene derivative (C9, Fig. 10) bearing long alkyl chains and two hydroxyl groups with anchoring function was used by Zhan *et al.* to modify the  $\text{SnO}_2$  ETL in planar n-i-p  $(\text{FAPbI}_3)_x(\text{MAPbBr}_3)_{1-x}$  PSCs, affording a PCE of 21.3%. C9 atop of the  $\text{SnO}_2$  ETL efficiently passivated oxygen vacancy-related defects on the  $\text{SnO}_2$  surface *via* the covalent bonding of under-coordinated Sn with terminal hydroxyl groups within C9. Moreover, the long and hydrophobic alkyl chain within C9 was beneficial for the ordered molecular self-assembly and forming a non-wetting surface for the perovskite film deposition, leading to the suppressed heterogeneous nucleation and enhanced crystallinity of the perovskite film.<sup>84</sup> In 2019, Chen *et al.* synthesized a pyrrolidinofullerene derivative ( $\text{NPC}_{60}\text{-OH}$ ) bearing phenolic hydroxyl (Fig. 10) and applied it to modify the  $\text{SnO}_2$  ETL in planar n-i-p PSCs. The reduced energy band gap between the  $\text{SnO}_2$  ETL and the perovskite film as well



**Fig. 11** (a) Schematic of the device structure with C<sub>60</sub>-SAM atop of the TiO<sub>2</sub> surface. Reproduced with permission from ref. 85. Copyright 2013, American Chemical Society. (b) Device structure of the device and schematic illustration for the crosslinking of C<sub>60</sub>-SAM with a silane-coupling agent. Reproduced with permission from ref. 88. Copyright 2018, Nature Publishing Group. (c) Schematic illustration of PSC structures with CPTA as the ETL. Reproduced with permission from ref. 92. Copyright 2017, Wiley-VCH. (d) Schematic illustration of PSC structures with C<sub>60</sub>-ETA. Reproduced with permission from ref. 97. Copyright 2016, Royal Society of Chemistry. (e) UV-visible absorption spectra of the corresponding films and the schematic illustration of fullerene derivatives coated ZnO NPs with core-shell structures. Reproduced with permission from ref. 99. Copyright 2019, Elsevier Inc.

as the increased grain size of the perovskite were realized *via* inserting NPC<sub>60</sub>-OH to modify the SnO<sub>2</sub> layer, leading to a high PCE of 21.39%.<sup>98</sup>

In 2019, Jen *et al.* reported a catechol-functionalized fullerene derivative (Fa, Fig. 10) which enables strong binding with ZnO *via* covalent bonding between the catechol within Fa and hydroxyl groups on the ZnO nanoparticle surface, resulting in the formation of fullerene-modified ZnO (Fa-ZnO) nanoparticles. On one hand, Fa-ZnO nanoparticles with quasi-core-shell structures facilitate the charge transfer from ZnO nanoparticles to fullerene derivatives *via* the Zn-O-C bonds, leading to the improved electron density in the conduction band of ZnO as well as the reduced work function and enhanced conductivity of Fa-ZnO nanoparticles (Fig. 11e). On the other hand, Fa-ZnO nanoparticles of the n-type heterojunction combined with p-type mesoscopic NiO<sub>x</sub> within the perovskite film enable the successful construction of inorganic p-n dual sensitized PSCs. As a result, the devices with CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> and FA<sub>0.85</sub>MA<sub>0.15</sub>-PbI<sub>2.55</sub>Br<sub>0.45</sub> light-absorbing layers afford PCE as high as 20.2% and 21.1%, respectively. Furthermore, the high-quality Fa-ZnO nanoparticle ETL greatly enhances the device long-term stability due to the reduced trap states, the inhibited ion migration and moisture diffusion.<sup>99</sup>

In order to compare the performance of different fullerene derivatives, the above-mentioned carboxyl and hydroxyl functionalized fullerene derivatives and their corresponding photovoltaic parameters are summarized in Table 3. The polar carboxyl and hydroxyl groups are able to anchor metal oxide ETLs to passivate the oxygen vacancy-related defects on the surface of metal oxide ETLs. The modification of metal oxide ETLs by these polar fullerene derivatives helps to achieve higher electron transport, suitable energy level alignments and reduced charge carrier recombination. Furthermore, the increased surface wettability after inserting these polar fullerene derivatives is beneficial for forming a continuous and compact perovskite film and suppressing the heterogeneous nucleation, affording a high-quality perovskite film with large grain size and optimized grain orientation for remarkably decreased trap states and increased charge carrier mobility. Besides, these polar fullerene derivatives have another role in acting as independent ETLs or double ETLs, in which fullerene derivatives enable the strong chemical interaction with ITO or FTO for matched energy level alignment and trap state passivation. Based on the advantages of these carboxyl or hydroxyl functionalized fullerene derivatives, modulating these

Table 3 Device performance of PSCs based on carboxyl and hydroxyl functionalized fullerene derivatives

| Compound                        | Active layer                                                                 | LUMO (eV) | $\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ) | Role of the molecule          | $J_{sc}$ (mA cm <sup>-2</sup> ) | $V_{oc}$ (V) | FF (%) | PCE (%) | Ref. |
|---------------------------------|------------------------------------------------------------------------------|-----------|----------------------------------------------------------|-------------------------------|---------------------------------|--------------|--------|---------|------|
| C <sub>60</sub> SAM             | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -3.95     | —                                                        | Modifying TiO <sub>2</sub>    | 22.1                            | 1.04         | 0.75   | 17.3    | 86   |
| 8                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -4.20     | —                                                        | Modifying TiO <sub>2</sub>    | 19.40                           | 0.79         | 76     | 10.8    | 87   |
| 9                               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -4.00     | —                                                        | Modifying TiO <sub>2</sub>    | 19.8                            | 0.85         | 71     | 11.7    | 87   |
| PCBA                            | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                             | -4.2      | —                                                        | Modifying TiO <sub>2</sub>    | 21.38                           | 1.16         | 72     | 17.76   | 89   |
| CPTA                            | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                             | -3.9      | 5.4 × 10 <sup>-3</sup>                                   | ETL                           | 22.06                           | 1.10         | 75.61  | 18.39   | 92   |
| CPTA                            | {en}FASnI <sub>3</sub>                                                       | -3.9      | —                                                        | Modifying SnO <sub>2</sub>    | 16.45                           | 0.687        | 65     | 7.40    | 94   |
| A <sub>10</sub> C <sub>60</sub> | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                             | -4.1      | —                                                        | Additive                      | 19.41                           | 0.88         | 81.6   | 13.97   | 90   |
| WS-C <sub>60</sub>              | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                             | -4.1      | —                                                        | Modifying PC <sub>61</sub> BM | 27.4                            | 0.95         | 56     | 14.6    | 91   |
| Fullerenol                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -4.27     | —                                                        | Modifying TiO <sub>2</sub>    | 21.28                           | 0.96         | 72     | 14.7    | 95   |
| f-C <sub>60</sub>               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -4.45     | —                                                        | ETL                           | 21.32                           | 1.04         | 76.25  | 16.97   | 96   |
| f-C <sub>70</sub>               | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>           | -4.42     | —                                                        | ETL                           | 21.21                           | 1.03         | 72.58  | 15.94   | 96   |
| C <sub>60</sub> -ETA            | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                             | -3.72     | —                                                        | ETL                           | 23.76                           | 1.06         | 69     | 18.49   | 96   |
| C9                              | (FAPbI <sub>3</sub> ) <sub>x</sub> (MAPbBr <sub>3</sub> ) <sub>1-x</sub>     | -4.03     | —                                                        | Modifying SnO <sub>2</sub>    | 24.1                            | 1.12         | 78.9   | 21.3    | 84   |
| NPC <sub>60</sub> -OH           | Perovskite                                                                   | -4.14     | —                                                        | Modifying SnO <sub>2</sub>    | 23.37                           | 1.13         | 80.73  | 21.39   | 98   |
| Fa                              | FA <sub>0.85</sub> MA <sub>0.15</sub> PbI <sub>2.55</sub> Br <sub>0.45</sub> | —         | —                                                        | Modifying ZnO                 | 22.83                           | 1.14         | 81     | 21.11   | 99   |

functional groups including the number and steric locations should be further investigated so as to improve their performance in PSCs.

## 5. Halogen functionalized fullerene derivatives

Interestingly, simple halogen atoms such as Cl, Br and F have been demonstrated to be magic elements in PSCs after being grafted onto the fullerene cage. Incorporating the halogen-functionalized fullerene derivatives into PSCs has been revealed to enlarge the grain size, reduce current-voltaic hysteresis, and increase the charge recombination resistance as well as the stability of the device.<sup>100–105</sup> In 2018, Wang *et al.* synthesized three fulleropyrrolidine derivatives with different substituents (H, Cl and Br) abbreviated as NAMF-H, NAMF-Cl and NAMF-Br (Fig. 12) to study the influence of halogen atoms within fullerene derivatives on the performance of planar n-i-p CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. Their results showed that NAMF-Cl applied as the interfacial layer atop the TiO<sub>2</sub> ETL in PSCs afforded the

best PCE of 19.3%, which was attributed to the better coplanarity of the functional group and higher electron mobility. Furthermore, the chlorine atom in NAMF-Cl was unveiled to interact with the TiO<sub>2</sub> ETL with the formation of a O=Ti-Cl bond, benefiting the defect passivation and the enlarged grain size.<sup>100</sup>

In particular, compounds containing fluorine atoms were usually evidenced to possess strong hydrophobicity and low surface energy which helps to improve the ambient stability of perovskites.<sup>101</sup> Therefore, introducing fluorinated groups into fullerene derivatives to form novel fluoro-functionalized fullerene derivatives is highly desirable. In 2016, Jen *et al.* reported a fluoroalkyl substituted hydrophilic fullerene (DF-C<sub>60</sub>, Fig. 12) which was applied as an additive of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite to construct fullerene/perovskite p-i-n BHJ-PSCs, yielding a PCE of 18.11% with increased stability and reduced trap-states. The incorporated DF-C<sub>60</sub> with low surface energy mainly located at the upper surface and grain boundaries of the perovskite film, helping to reduce the current-voltage hysteresis and passivate the defects as well as enhance the ambient stability.<sup>102</sup> One year later, the same group adopted an anti-solvent approach to

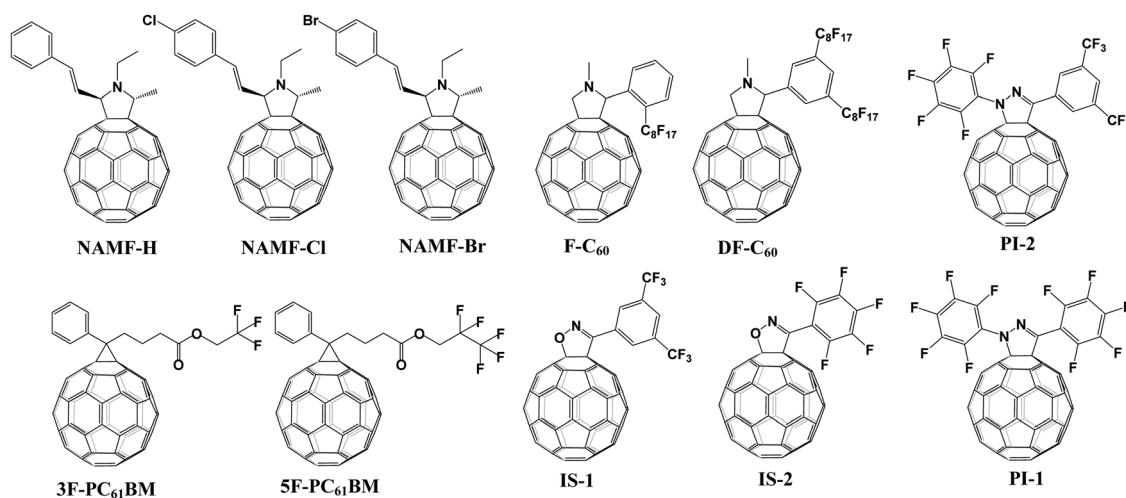


Fig. 12 Molecular structures of halogen functionalized fullerene derivatives applied in PSCs.

incorporate DF-C<sub>60</sub> into the low-bandgap Pb–Sn binary perovskite (CH<sub>3</sub>NH<sub>3</sub>Pb<sub>0.5</sub>Sn<sub>0.5</sub>I<sub>3</sub>) for the preparation of graded heterojunction PSCs. A graded distribution of DF-C<sub>60</sub> in the perovskite film effectively passivated defects, decreased the number of trap sites and improved the absorber quality, leading to an improved PCE of 15.61% and a high *V*<sub>oc</sub> (0.89 V).<sup>103</sup> Likewise, they also synthesized another novel fluoroalkyl substituted fullerene derivative (F-C<sub>60</sub>) with only one C<sub>8</sub>F<sub>17</sub> group (Fig. 12), and combined it with bis-C<sub>60</sub> to form a hybrid fullerene cathode interlayer in p–i–n PSCs. The hybrid fullerene cathode interlayer simultaneously possesses the advantage of F-C<sub>60</sub> and bis-C<sub>60</sub>, including the appealing electrical conductivity and lower surface energy which are beneficial for enhanced charge collection from the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3–x</sub>Cl<sub>x</sub> perovskite to the electrode and suppressed charge recombination in the perovskite light-absorbing layer. As a result, devices with a PCE of 15.5% and excellent stability retaining nearly 80% of their initial PCE after being exposed under ambient conditions (20% RH) for two weeks without any encapsulation were achieved.<sup>104</sup> In 2018, Su *et al.* synthesized two fluorinated PC<sub>61</sub>BM derivatives (3F-PC<sub>61</sub>BM and 5F-PC<sub>61</sub>BM, Fig. 12) and incorporated them as additives into the perovskite light-absorbing layer to study the effect of fluoroalkyl chain length within fullerene derivatives on the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite film quality and device performance. Incorporating 0.1 wt% of the 3F-PC<sub>61</sub>BM additive into the perovskite film enabled the formation of BHJ perovskite and densely packed perovskite grains, which helped to passivate the defects within the perovskite and suppress the permeation of moisture into the grain boundaries under ambient conditions. As a result, the devices with 3F-PC<sub>61</sub>BM additives afforded a PCE of 16.17%, which was much higher than that of the device based on 5F-PC<sub>61</sub>BM (8.65%). Besides, the device stability was improved after incorporating 3F-PC<sub>61</sub>BM, maintaining 80% of the initial efficiency after 550 hours of storage under ambient conditions (25 °C, 50% relative humidity). The results unveiled that 5F-PC<sub>61</sub>BM with a longer fluoroalkyl chain is prone to undergo self-aggregation more easily than that of 3F-PC<sub>61</sub>BM in the perovskite film, leading to a large amount of heterogeneous nucleation sites, which is responsible for the discontinuous rough film morphology with more voids.<sup>105</sup> In addition to the above fluoroalkyl chain substituted fullerene derivatives, the fluorine substituted phenyls were also used to functionalize fullerene, affording a variety of novel

fluoro-functionalized fullerene derivatives (IS-1, IS-2, PI-1 and PI-2, Fig. 12), which were applied to construct ETL-free PSCs based on perovskite:fullerene hybrid films. The as-prepared n–i–p PSCs based on the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>:IS-2 blend film exhibit the highest PCE of 14.3%.<sup>106</sup>

All of these halogen functionalized fullerene derivatives and their corresponding photovoltaic parameters are summarized in Table 4. We can conclude that grafting halogen atoms onto the fullerene cage generates some unique properties, rendering superior performance of the corresponding fullerene derivatives upon being applied as additives or modification layers in PSCs. Chlorine functionalized fullerene derivatives have the features of regulating the coplanarity of the pendent groups and interacting with TiO<sub>2</sub> to passivate defects. As for the fluorine functionalized fullerene derivatives, the introduced fluorine atoms are beneficial for improving the solubility of fullerene derivatives in polar solvents such as DMF for a facile fabrication procedure. On the other hand, fluorine substituted fullerene derivatives have low surface energy, helping to fabricate the grade heterojunction perovskite light-absorbing layer and to suppress the penetration of moisture into the grain boundaries of the perovskite for efficient and stable PSCs. Therefore, in order to address the inferior stability of PSCs based on organic lead halide perovskites, developing novel fluorine substituted hydrophobic fullerene derivatives appears to be an effective strategy to passivate the grain boundaries and improve the ambient stability simultaneously.

## 6. Cross-linked fullerene derivatives

### 6.1 Thermal cross-linked fullerene derivatives

In 2016, Snaith *et al.* applied two cross-linked fullerene derivatives (sol–gel C<sub>60</sub> and PCBCB, Fig. 13) as n-type charge collection layers in planar n–i–p CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3–x</sub>Cl<sub>x</sub> PSCs, leading to a PCE of 17.9% for both cross-linked fullerene ETLs. Cross-linked sol–gel C<sub>60</sub> *via* hydrolysis-condensation reactions and cross-linked PCBCB *via* annealing at 200 °C (Fig. 14a) could generate two types of insoluble fullerene films which are beneficial for the electron-selective contacts and reduced shunting paths toward improved hole-blocking and excellent charge transport ability.<sup>107</sup> In 2016, Liao *et al.* synthesized another thermal cross-linked fullerene derivative (C-PCBSD, Fig. 13) and

**Table 4** Device performance of PSCs based on halogen functionalized fullerene derivatives

| Compound               | Active layer                                                                       | LUMO (eV) | $\mu$ (cm <sup>2</sup> V <sup>−1</sup> s <sup>−1</sup> ) | Role of the molecule       | <i>J</i> <sub>sc</sub> (mA cm <sup>−2</sup> ) | <i>V</i> <sub>oc</sub> (V) | FF (%) | PCE (%) | Ref. |
|------------------------|------------------------------------------------------------------------------------|-----------|----------------------------------------------------------|----------------------------|-----------------------------------------------|----------------------------|--------|---------|------|
| NAMF-H                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.05     | $3.7 \times 10^{-4}$                                     | Modifying TiO <sub>2</sub> | 22.4                                          | 1.08                       | 78.4   | 19.0    | 100  |
| NAMF-Cl                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.08     | $1.44 \times 10^{-3}$                                    | Modifying TiO <sub>2</sub> | 22.7                                          | 1.08                       | 78.6   | 19.3    | 100  |
| NAMF-Br                | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.13     | $3.6 \times 10^{-4}$                                     | Modifying TiO <sub>2</sub> | 21.8                                          | 1.10                       | 79.7   | 19.1    | 100  |
| DF-C <sub>60</sub>     | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | —         | $1.8 \times 10^{-3}$                                     | Additive                   | 21.08                                         | 1.09                       | 78.7   | 18.11   | 102  |
| DF-C <sub>60</sub>     | CH <sub>3</sub> NH <sub>3</sub> Pb <sub>0.5</sub> Sn <sub>0.5</sub> I <sub>3</sub> | —         | —                                                        | Additive                   | 26.1                                          | 0.87                       | 69     | 15.61   | 103  |
| F-C <sub>60</sub>      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3–x</sub> Cl <sub>x</sub>                 | —         | $3.2 \times 10^{-4}$                                     | CBL                        | 21.2                                          | 0.97                       | 75.4   | 15.5    | 104  |
| 3F-PC <sub>61</sub> BM | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.2      | $5.61 \times 10^{-4}$                                    | Additive                   | 21.78                                         | 1.00                       | 73.34  | 16.17   | 105  |
| 5F-PC <sub>61</sub> BM | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.2      | $2.69 \times 10^{-4}$                                    | Additive                   | 14.99                                         | 0.87                       | 65.71  | 8.65    | 105  |
| IS-1                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.06     | —                                                        | Additive                   | 16.7                                          | 1.03                       | 69     | 11.8    | 106  |
| IS-2                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.05     | —                                                        | Additive                   | 16.1                                          | 1.06                       | 73.8   | 12.7    | 106  |
| IP-1                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.08     | —                                                        | Additive                   | —                                             | —                          | —      | —       | 106  |
| IP-2                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                   | −4.08     | —                                                        | Additive                   | 16.1                                          | 1.02                       | 69.4   | 11.7    | 106  |

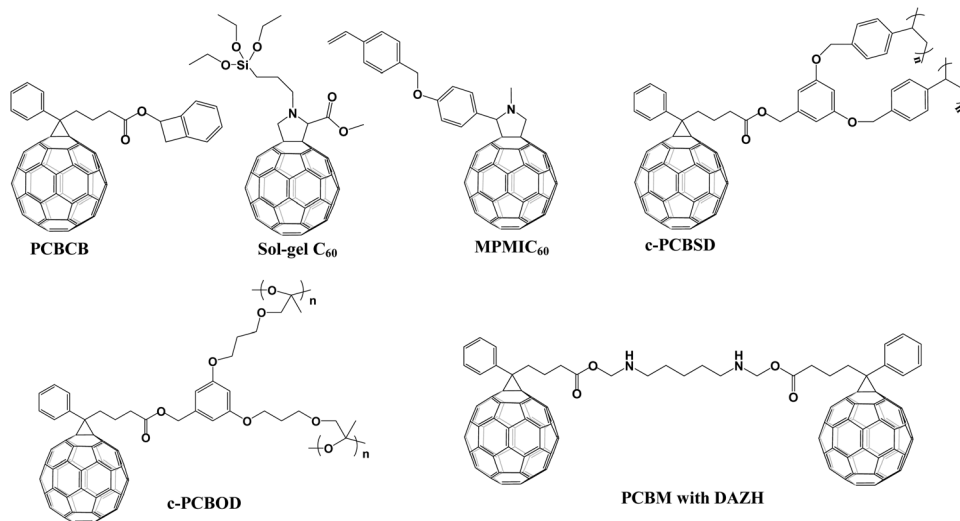


Fig. 13 Molecular structures of cross-linked fullerene derivatives applied in PSCs.

introduced it into the  $\text{CH}_3\text{NH}_3\text{PbI}_3\text{Cl}_{3-x}$  perovskite to enhance the crystallization of the perovskite film and electron extraction efficiency *via* an anti-solvent method. A cross-linked network of C-PCBSD could protect the perovskite layer from the erosion of moisture and passivate the defects in the bulk perovskite films, affording a PCE of 17.21%.<sup>108</sup> Later on, the same group prepared a face-on stacked composite film composed of a large  $\pi$ -conjugated graphdiyne (GD) and C-PCBSD *via*  $\pi$ - $\pi$  stacking interaction, which exhibited superior features including high electron mobility, efficient charge extraction and energy-level

tailoring. Moreover, the ordered orientation of the C-PCBSD/GD composite film (Fig. 14b) not only benefited the growth of the high-quality  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite film, but also provided sufficient solvent resistance to avoid the interfacial erosion during the process of depositing the perovskite precursor. Consequently, the PSC devices with C-PCBSD/GD composite films offered an improved PCE up to 20.19% and enhanced device stability.<sup>109</sup> In 2017, Petrozza *et al.* also applied C-PCBSD as an electron extraction layer atop the  $\text{TiO}_2$  ETL in planar n-i-p PSCs. *In situ* cross-linked C-PCBSD is vital for the interface

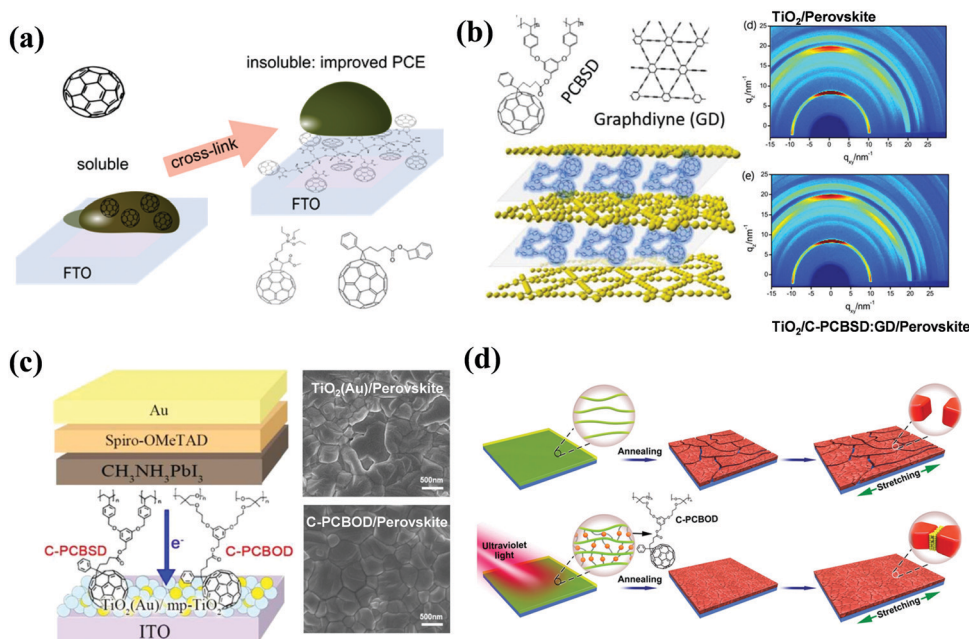


Fig. 14 (a) Schematic illustration of cross-linked processes. Reproduced with permission from ref. 107. Copyright 2016, American Chemical Society. (b) Schematic illustration for the face on stacked C-PCBSD film owing to the  $\pi$ - $\pi$  stacking interaction and the corresponding 2D GIXRD patterns. Reproduced with permission from ref. 109. Copyright 2017, Elsevier Ltd. (c) Schematic illustration of the device configuration and scanning electron microscopy (SEM) top-view images of the corresponding perovskite films. Reproduced with permission from ref. 112. Copyright 2017, American Chemical Society. (d) Operational mechanism of C-PCBOD. Reproduced with permission from ref. 113. Copyright 2019, Wiley-VCH.

energetics and the electronic quality of the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite layer, which contribute to the minimized carrier recombination losses. As a result, the device with a C-PCBSD electron extraction layer exhibited an obviously enhanced PCE close to 19% with a  $V_{\text{oc}}$  larger than 1.1 V.<sup>110</sup>

In addition to C-PCBSD, another thermal cross-linked styrene-functionalized fullerene derivative MPMIC<sub>60</sub> (Fig. 13) was synthesized to replace the traditional PC<sub>61</sub>BM and C<sub>60</sub> ETL in both regular and inverted PSCs. After annealing at 250 °C, MPMIC<sub>60</sub> could cross-link to form an insoluble solvent-resistant film with improved fracture resistance, leading to higher  $V_{\text{oc}}$  and  $J_{\text{sc}}$  values in planar n-i-p  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs.<sup>111</sup>

## 6.2 Photo cross-linked fullerene derivatives

In addition to thermal cross-linking with styrene groups as active sites, epoxy is another commonly used group which can undergo light-crosslinking under mild conditions. In 2017, Hsu *et al.* prepared a novel fullerene derivative (C-PCBOD, Fig. 13) and applied it as a cross-linkable material to modify the surface of the  $\text{TiO}_2$  ETL in n-i-p PSCs. The cross-linked PCBOD film formed *via* UV-curing provided a superior surface coverage toward the  $\text{TiO}_2$  ETL and a water-resistant layer to protect it from solvent erosion in the process of depositing the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite film. Cross-linked PCBOD between the  $\text{TiO}_2$  ETL and the perovskite layer passivated the trap-states of  $\text{TiO}_2$ , which was favorable for the excellent electron extraction and the retarded charge recombination (Fig. 14c), delivering an improved PCE of 15.9% and 18.3% for the compact  $\text{TiO}_2$  and mesoporous- $\text{TiO}_2$  ETL, respectively.<sup>112</sup>

In 2019, Liao *et al.* introduced a photo-crosslinked fullerene derivative (C-PCBOD) as a plasticizer (Fig. 14d) into the perovskite film, which distributes around the perovskite grain boundaries, leading to improved mechanical and moisture stability of the perovskite film. Furthermore, embracing the perovskite grain boundaries *via* C-PCBOD was able to passivate the defects and block the degradation of devices by suppressing the penetration of moisture along the perovskite grain boundaries. As a result, the  $\text{CH}_3\text{NH}_3\text{PbI}_3$  PSCs with C-PCBOD achieve a high PCE of 20.4% and 18.1% for rigid and flexible substrates, respectively.<sup>113</sup>

In 2017, a new cross-linked approach was reported by Cheyns *et al.*, in which 1,6-diazidohexane (DAZH, Fig. 13) as a bridge tether was utilized to cross-link the neighboring PC<sub>61</sub>BM for the preparation of cross-linked PC<sub>61</sub>BM through the highly

reactive nitrenes and C-H insertion. In addition to the outstanding electron extraction capability, the cross-linked PC<sub>61</sub>BM as the interlayer atop the  $\text{TiO}_2$  ETL shows excellent solvent-resistant ability for suppressing the wash away of the perovskite precursor toward the PC<sub>61</sub>BM interlayer in the process of spin-coating the perovskite film. The  $(\text{HC}(\text{NH}_2)_2)_{0.66}(\text{CH}_3\text{NH}_3)_{0.34}\text{PbI}_{2.85}\text{Br}_{0.15}$  PSCs with cross-linked interlayers afford a PCE of 18.4% and 14.9% for small-area devices and 4 cm<sup>2</sup> perovskite solar modules, respectively.<sup>114</sup>

Table 5 summarizes all reported cross-linked fullerene derivatives applied in PSCs and their corresponding photovoltaic parameters. Cross-linked fullerene derivatives have two merits including strong electron extraction capability and superior solvent-resistance, beneficial for improving the electron extraction from the perovskite film to the ITO electrode and enhancing the stability of the PSC device. It is well known that fullerene derivatives with superior electron extraction and transport ability have been widely applied as ETLs in planar p-i-n PSCs. However, the wash away of fullerene derivative ETLs from *N,N*-dimethylformamide (DMF) or dimethyl sulfoxide (DMSO) during the spin-coating process of the perovskite film is a critical issue to restrict the application of fullerene derivatives in planar n-i-p PSCs. Cross-linked fullerene derivatives provide an effective approach to address this issue. The incorporation of cross-linked fullerene derivatives into n-i-p PSCs is beneficial for improving the electron extraction from the perovskite film to the ITO electrode and enhancing the device stability. The as-formed organic networks of cross-linked fullerene derivatives can further improve mechanical stability and charge transfer of the device, resulting in enhanced device performance. However, the reported cross-linked fullerene derivatives applied in PSCs are still limited to styryl and epoxy. Therefore, developing new cross-linked fullerene derivatives bearing other cross-linkable groups is highly desirable toward improved device stability and flexible devices.

## 7. Other fullerene derivatives

Except for the abovementioned fullerene derivatives which can be classified clearly according to the functional groups, a number of other fullerene derivatives including ICBA and ICBA-like fullerene derivatives, fulleropyrrolidine derivatives and dimeric fullerene derivatives have been also applied in PSCs, which are described as follows, and their chemical

**Table 5** Device performance of PSCs incorporating cross-linked fullerene derivatives

| Compound                      | Active layer                                        | LUMO (eV) | $\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ) | Role of the molecule     | $J_{\text{sc}}$ (mA cm <sup>-2</sup> ) | $V_{\text{oc}}$ (V) | FF (%) | PCE (%) | Ref. |
|-------------------------------|-----------------------------------------------------|-----------|----------------------------------------------------------|--------------------------|----------------------------------------|---------------------|--------|---------|------|
| Sol-gel C <sub>60</sub>       | $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ | —         | $3.8 \times 10^{-4}$                                     | ETL                      | 23.0                                   | 1.07                | 73     | 17.9    | 107  |
| PCBCB                         | $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ | —         | $5.9 \times 10^{-3}$                                     | ETL                      | 22.4                                   | 1.11                | 73     | 17.9    | 107  |
| C-PCBSD                       | $\text{CH}_3\text{NH}_3\text{PbI}_3$                | —         | —                                                        | Modifying $\text{TiO}_2$ | 21.1                                   | 1.12                | 79.0   | 18.7    | 110  |
| C-PCBSD                       | $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ | —         | —                                                        | Additive                 | 22.81                                  | 0.98                | 77     | 17.21   | 108  |
| MPMIC <sub>60</sub>           | $\text{CH}_3\text{NH}_3\text{PbI}_3$                | -4.1      | —                                                        | ETL                      | 20.2                                   | 1.08                | 64     | 13.8    | 111  |
| C-PCBOD                       | $\text{CH}_3\text{NH}_3\text{PbI}_3$                | -3.8      | —                                                        | Modifying $\text{TiO}_2$ | 23.99                                  | 1.041               | 73.25  | 18.29   | 112  |
| C-PCBOD                       | $\text{CH}_3\text{NH}_3\text{PbI}_3$                | —         | —                                                        | Additive                 | 22.60                                  | 1.14                | 79     | 20.4    | 113  |
| PC <sub>61</sub> BM with DAZH | $\text{CH}_3\text{NH}_3\text{PbI}_3$                | —         | —                                                        | ETL                      | 20.3                                   | 1.08                | 77.9   | 17.1    | 114  |

Table 6 Device performance of PSCs incorporating some functionalized fullerene derivatives

| Compound                                | Active layer                                                                                                                       | LUMO (eV) | $\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ) | Role of the molecule       | $J_{sc}$ (mA cm <sup>-2</sup> ) | $V_{oc}$ (V) | FF (%) | PCE (%) | Ref. |
|-----------------------------------------|------------------------------------------------------------------------------------------------------------------------------------|-----------|----------------------------------------------------------|----------------------------|---------------------------------|--------------|--------|---------|------|
| ICBA                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.6      | $6.9 \times 10^{-3}$                                     | ETL                        | 10.03                           | 0.58         | 58     | 3.4     | 33   |
| ICTA                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | —         | —                                                        | ETL                        | 22.1                            | 1.10         | 74.2   | 18.04   | 118  |
| IPB                                     | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.94     | —                                                        | ETL                        | 16.28                           | 1.102        | 78     | 14.02   | 46   |
| IPH                                     | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.94     | —                                                        | ETL                        | 16.70                           | 1.107        | 79     | 14.64   | 46   |
| C <sub>60</sub> (CH <sub>2</sub> )(Ind) | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.66     | $3.0 \times 10^{-3}$                                     | ETL                        | 20.4                            | 1.13         | 80     | 18.1    | 119  |
| C5-NCMA                                 | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.87     | $1.59 \times 10^{-3}$                                    | ETL                        | 20.68                           | 1.08         | 79.1   | 17.6    | 120  |
| EDNC                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.86     | $8.5 \times 10^{-5}$                                     | ETL                        | 19.85                           | 0.95         | 66.92  | 12.64   | 121  |
| BDNC                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.86     | $7.7 \times 10^{-5}$                                     | ETL                        | 16.17                           | 0.93         | 48.72  | 7.36    | 121  |
| IBF-Ep                                  | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                                                                 | -4.40     | —                                                        | ETL                        | 16.9                            | 0.86         | 62     | 9.0     | 122  |
| C <sub>60</sub> (9MA)                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | —         | —                                                        | ETL                        | 21.1                            | 0.984        | 72.3   | 15.0    | 123  |
| ICMA                                    | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.85     | —                                                        | ETL                        | 20.0                            | 1.07         | 64.7   | 13.9    | 124  |
| DMEC <sub>60</sub>                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.89     | $7.21 \times 10^{-4}$                                    | ETL                        | 21.73                           | 0.92         | 75.8   | 15.2    | 125  |
| DMEC <sub>70</sub>                      | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.90     | $9.07 \times 10^{-4}$                                    | ETL                        | 22.44                           | 0.95         | 77.1   | 16.4    | 125  |
| C <sub>60</sub> MC <sub>12</sub>        | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Br <sub>x</sub>                                                                 | -4.16     | —                                                        | ETL                        | 17.45                           | 1.24         | 77     | 16.74   | 47   |
| Bis-DMEC <sub>60</sub>                  | (5-AVA) <sub>0.03</sub> (MA) <sub>0.97</sub> PbI <sub>3</sub>                                                                      | -3.80     | —                                                        | Modifying TiO <sub>2</sub> | 23.30                           | 0.92         | 71     | 15.21   | 126  |
| DPC <sub>60</sub>                       | CS <sub>0.05</sub> (MA <sub>0.17</sub> FA <sub>0.83</sub> ) <sub>0.95</sub> Pb(I <sub>0.83</sub> Br <sub>0.17</sub> ) <sub>3</sub> | -3.9      | $1.03 \times 10^{-3}$                                    | Modifying SnO <sub>2</sub> | 23.0                            | 1.14         | 77.7   | 20.4    | 127  |
| CPTA-E                                  | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -4.18     | $3.8 \times 10^{-4}$                                     | ETL                        | 20.22                           | 1.103        | 78.22  | 17.44   | 128  |
| PDI-C <sub>60</sub>                     | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.96     | $8.76 \times 10^{-4}$                                    | ETL                        | 22.1                            | 1.061        | 79.2   | 18.6    | 129  |
| D-C <sub>60</sub>                       | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>                                                                                   | -3.88     | $9.83 \times 10^{-4}$                                    | ETL                        | 21.89                           | 0.96         | 78.8   | 16.6    | 131  |
| d-PC <sub>61</sub> BM                   | CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3-x</sub> Cl <sub>x</sub>                                                                 | —         | —                                                        | ETL                        | 16.70                           | 0.941        | 73     | 11.43   | 130  |

structures along with the corresponding photovoltaic parameters are summarized in Table 6.

### 7.1 ICBA and ICBA-like fullerene derivatives

In 2013, Chen *et al.* first applied the indene-C<sub>60</sub> bisadduct (IC<sub>60</sub>BA, Fig. 15) as an ETL of planar p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, which afforded a low PCE of 3.4%.<sup>33</sup> In 2015, Jen *et al.* also used IC<sub>60</sub>BA as the ETL in planar p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs in which the IC<sub>60</sub>BA ETL was modified by the bis-C<sub>60</sub> layer, achieving a PCE of 8.06%.<sup>115</sup> In 2016, Chang *et al.* deposited the IC<sub>60</sub>BA ETL atop the CH<sub>3</sub>NH<sub>3</sub>PbBr<sub>3</sub> light-absorbing layer to form a pseudo BHJ structure by the penetration of IC<sub>60</sub>BA into the defects/voids of the CH<sub>3</sub>NH<sub>3</sub>PbBr<sub>3</sub> film. The devices combining the IC<sub>60</sub>BA ETL and solvent annealing procedure afforded a PCE of 7.50% and a high  $V_{oc}$  of 1.60 V.<sup>116</sup> In 2017, Huang *et al.* applied the isomeric pure IC<sub>60</sub>BA-tran3 as the ETL to construct wide-bandgap (FA<sub>0.83</sub>MA<sub>0.17</sub>)<sub>0.95</sub>CS<sub>0.05</sub>Pb(I<sub>0.6</sub>Br<sub>0.4</sub>)<sub>3</sub> PSCs, accomplishing a high PCE of 18.5% with a high  $V_{oc}$  of 1.21 V. The superiority of IC<sub>60</sub>BA-tran3 relative to the IC<sub>60</sub>BA-mixture is due to the reduced energy disorder and the increased conductivity, consequently improving the device efficiency of PSCs.<sup>117</sup> Moreover, Neher *et al.* pointed out that the indene-C<sub>60</sub>-trisadduct (ICTA, Fig. 15) with the lowest electron affinity applied as an ETL of planar p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs is responsible for the highest  $V_{oc}$  among C<sub>60</sub>, PC<sub>61</sub>BM and ICTA ETLs. The higher LUMO energy level of ICTA than those of PC<sub>61</sub>BM and C<sub>60</sub> ETLs leads to an efficient reduction of  $V_{oc}$  losses due to the proper energy alignment, exhibiting an improved PCE of 18.04% and a  $V_{oc}$  of 1.1 V.<sup>118</sup>

In addition to IC<sub>60</sub>BA, a series of IC<sub>60</sub>BA-like fullerene derivatives were developed to act as ETLs in PSCs. In 2016, Bolink *et al.* unveiled that two IC<sub>60</sub>BA-like fullerene derivatives (IPB, IPH, Fig. 15) bearing, respectively, butyl and hexyl ester can form high quality ETLs with fewer defects in p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, resulting in enhanced  $J_{sc}$  and  $V_{oc}$ . The device with IPB and IPH ETLs exhibited improved PCEs of

14.02% and 14.64%, respectively.<sup>46</sup> Later on, Cao *et al.* synthesized a IC<sub>60</sub>BA-like fullerene derivative C<sub>60</sub>(CH<sub>2</sub>)(Ind) (Fig. 15). The incorporation of C<sub>60</sub>(CH<sub>2</sub>)(Ind) as the ETL in p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs enables more efficient interfacial defect passivation, improved electron extraction and suppressed trap-assisted recombination (Fig. 16a), leading to an outstanding PCE of 18.1% and  $V_{oc}$  of 1.13 V which are higher than those of the PC<sub>61</sub>BM-based device (16.2% and 1.05 V). The improved  $V_{oc}$  is obtained from the higher LUMO energy levels (-3.66 V) of C<sub>60</sub>(CH<sub>2</sub>)(Ind) than that of PC<sub>61</sub>BM (-3.8 eV).<sup>119</sup> Another IC<sub>60</sub>BA-like fullerene derivative (C5-NCMA, Fig. 15) with two pentyloxy chains was synthesized by Yang *et al.* and used as the ETL to replace the PC<sub>61</sub>BM ETL in planar inverted PSCs. Due to the higher LUMO energy level and more efficient electron extraction/electron transport of the C5-NCMA ETL than that of PC<sub>61</sub>BM, the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSC devices delivered an improved PCE of 17.6% with negligible hysteresis.<sup>120</sup> Similarly, Xie *et al.* prepared two fullerene derivatives (EDNC and EBNC, Fig. 15) in 2017, which have similar structures to that of C5-NCMA except for the number of pendent chains, and applied it as the ETL in p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. The devices with EDNC and EBNC ETLs achieved PCEs of 12.64% and 7.36%, respectively, which are however lower than that of the device with the PC<sub>61</sub>BM ETL (15.04%). The inferior performance of EDNC and EBNC relative to that of C5-NCMA indicates that the minor tailoring of the functional groups within such fullerene derivatives can lead to a distinct performance difference.<sup>121</sup>

Gradečak *et al.* used the Diels-Alder reaction to synthesize a new fullerene derivative isobenzofulvene-C<sub>60</sub>-epoxide (IBF-Ep, Fig. 15) and used it as the ETL to replace the PC<sub>61</sub>BM ETL in both n-i-p and p-i-n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> PSCs. Due to the bulky epoxidized isobenzofulvene appendage which is beneficial for suppressing solid state phase transitions, the IBF-Ep ETL exhibits excellent morphological stability under thermal stress and good compatibility with the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3-x</sub>Cl<sub>x</sub> perovskite, leading to a PCE of 9.0% for p-i-n PSCs.<sup>122</sup> Another soluble

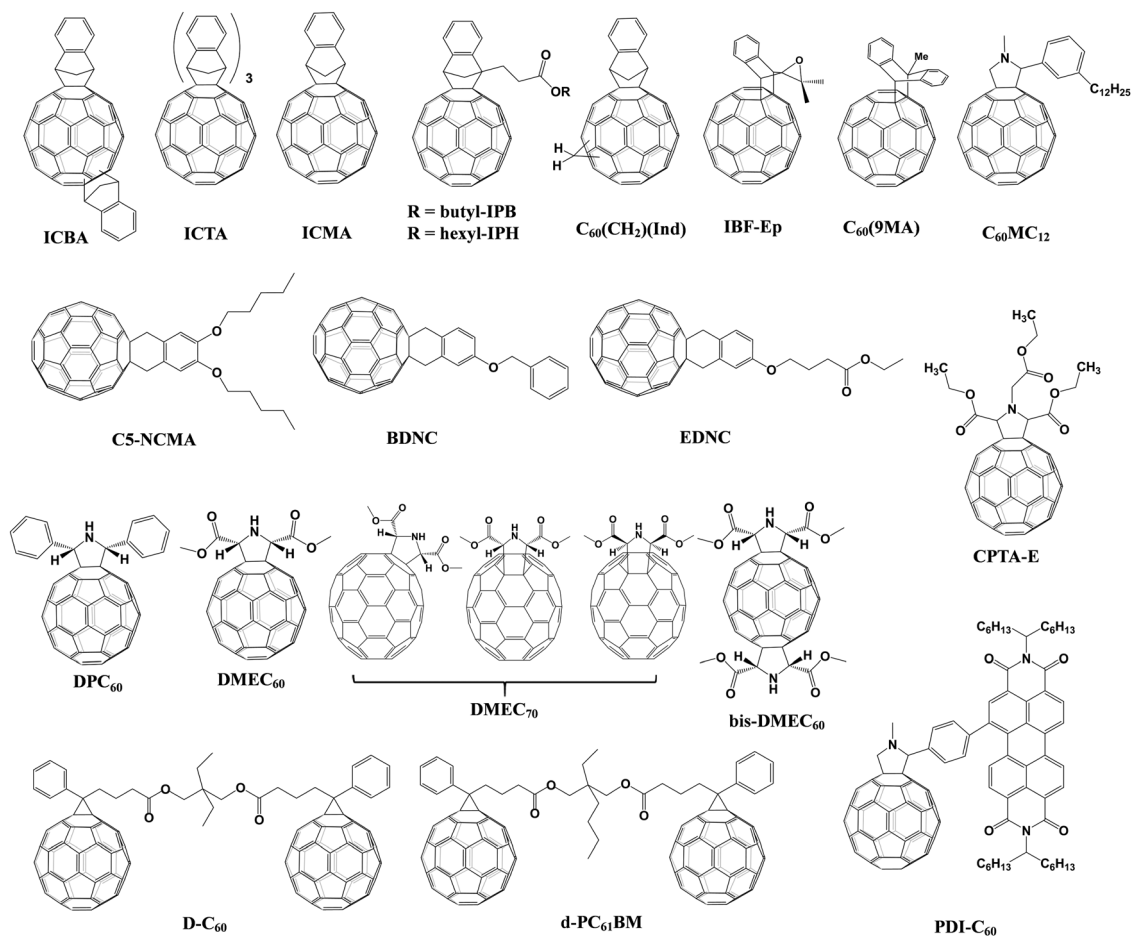


Fig. 15 Molecular structures of other functionalized fullerene derivatives applied in PSCs.

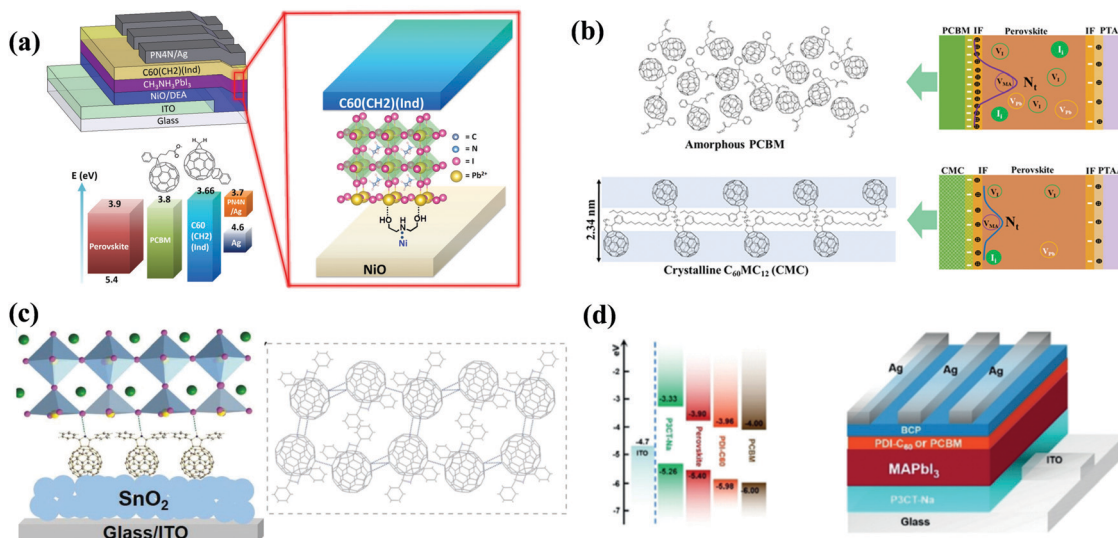


Fig. 16 (a) Schematic illustration of PSC structures and energy-level. Reproduced with permission from ref. 119. Copyright 2017, Wiley-VCH. (b) Schematic illustration of the mechanism involving crystalline fullerene derivatives for enhancement in device performances. Reproduced with permission from ref. 47. Copyright 2018, American Chemical Society. (c) Schematic illustration of interfacial modification and the corresponding molecular packing. Reproduced with permission from ref. 127. Copyright 2019, Wiley-VCH. (d) Corresponding energy-level diagram and device structures of PSCs. Reproduced with permission from ref. 129. Copyright 2019, Wiley-VCH.

fullerene derivative C<sub>60</sub>-9-methylantracene mono-adduct (C<sub>60</sub>(9MA), Fig. 15) synthesized *via* the Diels–Alder reaction was developed by Imahori *et al.* and was used as a thermal precursor to the C<sub>60</sub> electron selective layer (ESL) in planar n–i–p CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs. The superior film-forming property by using the thermal precursor approach afforded a remarkably improved FF (72.3%) and a PCE (15.0%) of the device relative to that of the TiO<sub>2</sub>-based device (FF of 67.1% and PCE of 12.9%).<sup>123</sup> In 2017, Albrecht *et al.* systematically studied the influence of fullerene derivative (C<sub>60</sub>, PC<sub>61</sub>BM, ICMA) ETLs on the device performance of n–i–p PSCs. They found that the devices with independent ICMA ETLs (Fig. 15) exhibited an averaged PCE of 13.9%, while those based on TiO<sub>2</sub>/PC<sub>61</sub>BM double-layer ETLs afforded a stabilized PCE of 18.0% and negligible photocurrent hysteresis. The undesirable PCE of the ICMA ETL is perhaps attributed to the lower LUMO energy level of approximately –3.85 eV than that of the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite (–3.9 eV), which could induce a small charge extraction barrier when attaching the perovskite, delivering a reduced efficiency.<sup>124</sup>

## 7.2 Fulleropyrrolidine derivatives

Several fulleropyrrolidine derivatives synthesized *via* a one-step 1,3-dipolar cycloaddition reaction (*i.e.*, the Prato reaction) were demonstrated to be efficient ETLs applied in PSCs as well. In 2016, Echegoyen *et al.* synthesized two fullerene derivatives including 2,5-(dimethyl ester) C<sub>60</sub> fulleropyrrolidine (DMEC<sub>60</sub>) and the analogous C<sub>70</sub> derivative (DMEC<sub>70</sub>, Fig. 15) and applied them as ETLs to replace the PC<sub>61</sub>BM ETL in inverted PSCs. Due to the suitable LUMO energy level and higher electron mobility as well as the excellent electron extraction capability resulted from the interactions between the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite and the addend groups on fullerene derivatives, the devices based on DMEC<sub>60</sub> and DMEC<sub>70</sub> ETLs exhibited improved PCEs of 15.2% and 16.4%, respectively, which are both higher than those of devices based on PC<sub>61</sub>BM ETLs (14.5%) and PC<sub>71</sub>BM ETLs (15.0%).<sup>125</sup> Later on, Han *et al.* synthesized a high-symmetric bis-adduct of DMEC<sub>60</sub> (bis-DMEC<sub>60</sub>, Fig. 15) and incorporated it into printable mesoscopic PSCs, achieving an improved PCE of 15.21% with negligible hysteresis relative to that of the control device without bis-DMEC<sub>60</sub> (13.01%). The strong chemical interaction between the perovskite and the incorporated bis-DMEC<sub>60</sub> improves the conductivity of the (5-AVA)<sub>0.03</sub>(MA)<sub>0.97</sub>PbI<sub>3</sub> perovskite film and facilitates the defect passivation at the grain boundaries effectively.<sup>126</sup> In 2018, Khadka *et al.* developed an approach to tailor the performance of wide-band-gap CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3–x</sub>Br<sub>x</sub> PSCs with highly crystalline fulleropyrrolidine derivatives (C<sub>60</sub>MC<sub>12</sub>, Fig. 15). Compared to the amorphous PC<sub>61</sub>BM, the higher crystallinity of long-chain alkyl-substituted C<sub>60</sub>MC<sub>12</sub> is beneficial for mitigating the energy disorder (Fig. 16b) and soothing the recombination activities, contributing to the improved PCE of 16.74% and a high V<sub>oc</sub> of 1.24 V.<sup>47</sup> More recently, Wei *et al.* applied 2,5-diphenyl C<sub>60</sub> fulleropyrrolidine (DPC<sub>60</sub>) as a modification layer sandwiched between SnO<sub>2</sub> and the Cs<sub>0.05</sub>(MA<sub>0.17</sub>FA<sub>0.83</sub>)<sub>0.95</sub>Pb(I<sub>0.83</sub>Br<sub>0.17</sub>)<sub>3</sub> perovskite in planar n–i–p PSCs, achieving a PCE of 20.4% along with excellent photothermal stability (Fig. 16c). The enhanced performance of PSCs is obtained from the inserted DPC<sub>60</sub> interlayer that

affords appropriate energy levels, and the improved electron mobility of the DPC<sub>60</sub> film is due to the short distance between two adjacent fullerene cages, the chemical interaction with the perovskite layer, and low solubility in the perovskite solvents. Besides, the chemical interaction between N–H and I at the DPC<sub>60</sub>/perovskite interface endowed the PSCs with enhanced defect passivation and reduced charge recombination. Furthermore, the smooth and hydrophobic DPC<sub>60</sub> layer helps to reduce heterogeneous nucleation and to improve the perovskite film quality, resulting in excellent photothermal stability.<sup>127</sup> A similar high-symmetry fulleropyrrolidine derivative such as C<sub>60</sub> pyrrolidine tris-acid ethyl ester (CPTA-E, Fig. 15) was applied as an ETL in planar p–i–n PSCs by Fang *et al.* The strong chemical interaction between CPTA-E and the perovskite through the coordination interaction of carboxylic ester groups with Pb<sup>2+</sup> ions enhances the adhesion of CPTA-E on the surface of CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>, facilitating the formation of a uniform and full covering ETL which prevents the direct contact of the perovskite and metal electrodes. As a result, the device delivered a PCE of 17.44% with suppressed hysteresis and prolonged stability due to the reduced charge recombination at the perovskite/electrode interface.<sup>128</sup> More recently, Yang *et al.* synthesized a novel fulleropyrrolidine derivative bearing perylene diimide (PDI-C<sub>60</sub>, Fig. 15) and used it as an ETL in inverted PSCs. Attaching the PDI group with large conductivity and high mobility onto the C<sub>60</sub> cage enables the PDI-C<sub>60</sub> ETL to possess a more matched energy level with the CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> perovskite, more efficient charge extraction/transport and reduced recombination rate. Therefore, the devices based on PDI-C<sub>60</sub> ETLs and PDI-C<sub>60</sub> interlayers exhibit high PCEs of 18.6% and 20.2%, respectively (Fig. 16d). Furthermore, the better device stability after incorporating the PDI-C<sub>60</sub> ETL results from the higher hydrophobic properties of PDI-C<sub>60</sub>.<sup>129</sup>

## 7.3 Dimeric fullerene derivatives

All of the abovementioned fullerene derivatives are mostly based on monoadducts and bisadducts of the monomeric fullerene cage. Alternatively, several dimeric fullerene derivatives have also been applied as ETLs in p–i–n PSCs to improve the device performance and stability simultaneously. In 2016, Ai *et al.* prepared a dumb-belled PC<sub>61</sub>BM dimer (d-PC<sub>61</sub>BM, Fig. 15) which was blended with PC<sub>61</sub>BM to form a hybrid ETL. Subsequently, the d-PC<sub>61</sub>BM/PC<sub>61</sub>BM blend ETL with an optimized ratio of PC<sub>61</sub>BM : d-PC<sub>61</sub>BM = 4 : 1 showed the capability of decreasing charge recombination, improving electron extraction, and adjusting the ETL morphology and CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3–x</sub>Cl<sub>x</sub> perovskite/ETL interface. As a result, the p–i–n PSCs with d-PC<sub>61</sub>BM/PC<sub>61</sub>BM blended ETLs exhibited a PCE of 11.43%, which is higher than that of the control device based on the PC<sub>61</sub>BM ETL (10.34%).<sup>130</sup> Likewise, Echegoyen *et al.* synthesized an analogous dimeric fullerene derivative (D-C<sub>60</sub>, Fig. 15) in 2017, in which two PC<sub>61</sub>BM moieties were linked together through the bridge molecule of 2,2-diethyl-1,3-propanediol. D-C<sub>60</sub> was applied as the ETL in planar p–i–n CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> PSCs, leading to a PCE of 16.6%, which is obviously higher than that of the control device with the PC<sub>61</sub>BM ETL (14.7%). The D-C<sub>60</sub> ETL shows several advantages such as appropriate energy

levels, high electron mobility and easy solution processability. Furthermore, D-C<sub>60</sub> can form a more hydrophobic and compact layer, which is beneficial for the improved device stability.<sup>131</sup>

## 8. Summary and outlook

During the rapid evolution of PSCs, fullerene derivatives with high electron affinity and strong electron accepting ability have played a crucial role in improving both the device performance and stability. Although the pristine fullerenes such as C<sub>60</sub> and C<sub>70</sub> possess strong electron extraction and electron transport ability, their relatively low solubilities in organic solvents limit applications in PSCs. Fortunately, functionalized fullerene derivatives have improved solubilities due to the grafting of the functional groups; thus they have been widely utilized in PSCs by means of being incorporated as interfacial materials between the perovskite layer and the electrode or as additives within the perovskite layer. As reviewed elaborately here, so far versatile functional groups, including polar groups (amino-, oligoether- and crown-ether), heterocyclic groups (pyridine and thiophene), the carboxyl (–COOH) group, the hydroxyl (–OH) group and halogen atoms, have been successfully grafted onto fullerene cages, affording a series of novel mono- or bis-adducts of fullerene derivatives, which have been extensively applied as either interlayers or additives in PSCs. In particular, unique fullerene derivatives bearing the cross-linkable groups (styryl and epoxy groups) can form insoluble cross-linked fullerene networks, and this enables the suppression of the wash away of the fullerene derivative ETL from DMF solvents during the process of perovskite precursor deposition. Besides, such fullerene derivatives have been incorporated as additives into PSCs and crosslinked into the insoluble network at the perovskite grain boundaries, contributing to improved device performance and stability. Moreover, with judicious molecular designs, fullerene derivatives with the perfect combination of the functional groups and fullerene cages may enable a reduced work function of metal cathodes, enhanced charge extraction/transfer, improved trap state/defect passivation and prolonged device stability.

Developing novel fullerene derivatives for further improving the device efficiency and stability of PSCs is still highly desirable yet challenging, because of the difficulty in the precise control on high-selectivity grafting of the suitable functional groups and their addition patterns, which are nevertheless critical and required for their high performance in PSCs. In addition, the in-depth mechanistic understanding of the correlation between the chemical structures of fullerene derivatives especially the functional groups and their effects on each photovoltaic parameter of PSCs is still needed, which can undoubtedly guide the design of novel fullerene derivatives. In particular, Lewis base functionalized fullerene derivatives especially those based on heterocyclic pyridine and thiophene moieties may render strong coordination interactions with Pb<sup>2+</sup> ions of the perovskite, thus leading to effective passivation of the trap states and promoted charge transport. An intriguing

question is whether other heterocyclic groups such as furan, imidazole, thiazole, or triazine can afford even stronger interactions with the perovskite or not. In addition, given that the fullerene cage is highly adjustable and the electronic properties of fullerenes can be readily tailored by varying their cage size or endohedral species,<sup>132</sup> other types of fullerenes with larger cage size and endohedral fullerenes can be utilized to construct novel fullerene derivatives with suitable energy levels and interactions with the perovskite and/or metal oxide layers. Furthermore, the structural tunability of fullerene derivatives promises their potential applications in large-area or flexible PSCs.

## Conflicts of interest

There are no conflicts to declare.

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